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REVISION HISTORY

REVISION NUMBER	REVISION DATE	DESCRIPTION	PAGES CHANGED
0	12/24	Initial release	—

SPECIFICATIONS

Table 1. Electrical Characteristics

(Specifications are at $T_J = -40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$ for the minimum and maximum values, $T_A = 25^{\circ}\text{C}$ for the typical values, $V_{BIAS} = 12\text{V}$, $RUN1$ and $RUN2 = 5\text{V}$, $VPRG1 = \text{Float}$, $EXTV_{CC} = 0\text{V}$, $DRVSET = 0\text{V}$, $DRVUV = 0\text{V}$, $DTCA$ and $DTCB = 0\text{V}$, unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS/COMMENTS	MIN	TYP	MAX	UNITS
Input Supply						
Bias Input Supply Operating Range	V_{BIAS}		4		100	V
Boost Converter Input Supply Operating Range	V_{IN}	$V_{BIAS} \geq 4\text{V}$	1		60	V
Output Voltage Operating Range	$V_{OUT1,OUT2}$		1.2		100	V
Controller Operation						
Channel 1 Regulated Feedback Voltage	V_{FB1}	$V_{BIAS} = 4\text{V to }100\text{V}$, ITH1 Voltage = 0.6V to 1.2V VPRG1 = floating, $T_A = 25^{\circ}\text{C}$	1.188	1.2	1.212	V
		VPRG1 = floating	1.182	1.2	1.218	V
		VPRG1 = 0V	23.45	24	24.55	V
		VPRG1 = $INTV_{CC}$	27.38	28	28.62	V
Channel 2 Regulated Feedback Voltage ¹	V_{FB2}	$V_{BIAS} = 4\text{V to }100\text{V}$, ITH2 Voltage = 0.6V to 1.2V $T_A = 25^{\circ}\text{C}$	1.188	1.2	1.212	V
			1.182	1.2	1.218	V
Channel 1 Feedback Current ¹		VPRG1 = floating, $T_A = 25^{\circ}\text{C}$ VPRG1 = 0V or $INTV_{CC}$	-50	0 2	+50	nA μA
Channel 2 Feedback Current ¹		$T_A = 25^{\circ}\text{C}$	-50	0	+50	nA
Feedback Overvoltage Threshold		Relative to V_{FBX} , $T_A = 25^{\circ}\text{C}$	7	10	13	%
Transconductance Amplifier ¹	g_{m1}, g_{m2}	ITH1 and ITH2 = 1.2V, Sink and Source = $5\mu\text{A}$		1.8		mmho
Maximum Current Sense Threshold	$V_{SENSE(MAX)}$	$V_{FBX} = 1.1\text{V}$, $SENSEX^+ = 12\text{V}$ ILIM = 0V	21	25	31	mV
		ILIM = floating	45	50	55	mV
		ILIM = $INTV_{CC}$	67	75	83	mV

(Specifications are at $T_J = -40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$ for the minimum and maximum values, $T_A = 25^{\circ}\text{C}$ for the typical values, $V_{BIAS} = 12\text{V}$, $RUN1$ and $RUN2 = 5\text{V}$, $VPRG1 = \text{Float}$, $EXTV_{CC} = 0\text{V}$, $DRVSET = 0\text{V}$, $DRVUV = 0\text{V}$, $DTCA$ and $DTCB = 0\text{V}$, unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS/COMMENTS	MIN	TYP	MAX	UNITS
Current Sense Threshold Matching between Channels		$V_{FBX} = 1.1\text{V}$, $SENSEx^+ = 12\text{V}$, $ILIM = \text{floating}$, $T_A = 25^{\circ}\text{C}$	-3.5	0	3.5	mV
SENSE1 ⁻ and SENSE2 ⁻ Pin Current	I_{SENSE1^-} , I_{SENSE2^-}	SENSE1 ⁻ and SENSE2 ⁻ = 12V, $T_A = 25^{\circ}\text{C}$	-1		+1	μA
SENSE1 ⁺ Pin Current	I_{SENSE1^+}	SENSE1 ⁺ < 3V $3.3\text{V} \leq \text{SENSE1}^+ < \text{INTV}_{CC} - 0.5\text{V}$ SENSE1 ⁺ > $\text{INTV}_{CC} + 0.5\text{V}$		1 75 725		μA μA μA
SENSE2 ⁺ Pin Current	I_{SENSE2^+}	SENSE2 ⁺ < $\text{INTV}_{CC} - 0.5\text{V}$, $T_A = 25^{\circ}\text{C}$ SENSE2 ⁺ > $\text{INTV}_{CC} + 0.5\text{V}$	-2	650	+2	μA μA
Soft-Start Charge Current		SS1 and SS2 = 0V	9.5	12	14.5	μA
RUN Pin ON Threshold		RUNx rising	1.15	1.20	1.25	V
RUN Pin Hysteresis				120		mV

DC Supply Current

V_{BIAS} Shutdown Current		$RUN1$ and $RUN2 = 0\text{V}$		1		μA
V_{BIAS} Sleep Mode Current		SENSE1 ⁺ < 3.2V, $EXTV_{CC} = 0\text{V}$ One Channel On Both Channels On		15 19		μA μA
Sleep Mode Current ² , Only Channel 1 On V_{BIAS} Current V_{BIAS} Current $EXTV_{CC}$ Current SENSE1 ⁺ Current		SENSE1 ⁺ $\geq 3.2\text{V}$, $EXTV_{CC} = 0\text{V}$ SENSE1 ⁺ $\geq 3.2\text{V}$, $EXTV_{CC} \geq 4.8\text{V}$ SENSE1 ⁺ $\geq 3.2\text{V}$, $EXTV_{CC} \geq 4.8\text{V}$ SENSE1 ⁺ $\geq 3.2\text{V}$		5 1 6 10		μA μA μA μA
Sleep Mode Current ² Both Channels On V_{BIAS} Current $EXTV_{CC}$ Current SENSE1 ⁺ Current		SENSE1 ⁺ $\geq 3.2\text{V}$, $EXTV_{CC} \geq 4.8\text{V}$		1 7 12		μA μA μA

(Specifications are at $T_J = -40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$ for the minimum and maximum values, $T_A = 25^{\circ}\text{C}$ for the typical values, $V_{BIAS} = 12\text{V}$, RUN1 and $\text{RUN2} = 5\text{V}$, $\text{VPRG1} = \text{Float}$, $\text{EXTV}_{CC} = 0\text{V}$, $\text{DRVSET} = 0\text{V}$, $\text{DRVUV} = 0\text{V}$, DTCA and $\text{DTCB} = 0\text{V}$, unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS/COMMENTS	MIN	TYP	MAX	UNITS
Pulse-Skipping (PS) Mode or Forced Continuous Mode (FCM), V_{BIAS} or EXTV_{CC} Current ²		One Channel On Both Channels On		2 3		mA mA

Gate Drivers

TGxxx or BGxxx On Resistance		$\text{DRVSET} = \text{INTV}_{CC}$ Pull-Up Pull-Down		1.0 1.0		Ω Ω
BOOSTx to DRV_{CC} Switch on Resistance		$\text{DRVSET} = \text{INTV}_{CC}$		6		Ω
TGxxx or BGxxx Transition Time ³		Rise Time Fall Time		25 15		ns ns
BGxxx Off to TGxxx on Adaptive Delay Time ⁴		$\text{DTCA} = 0\text{V}$		15		ns
TGxxx Off to BGxxx on Adaptive Delay Time ⁴		$\text{DTCB} = 0\text{V}$		15		ns
BGxxx Off to TGxxx on Open-Loop Delay ⁴		$\text{DTCA} = 10\text{k}\Omega$ $\text{DTCA} = 50\text{k}\Omega$ $\text{DTCA} = 100\text{k}\Omega$		7 25 40		ns ns ns
TGxxx Off to BGxxx on Open-Loop Delay ⁴		$\text{DTCB} = 10\text{k}\Omega$ $\text{DTCB} = 50\text{k}\Omega$ $\text{DTCB} = 100\text{k}\Omega$		7 25 40		ns ns ns
BGxxx Minimum On-Time ⁵	$t_{\text{ON(MIN)}}$			100		ns
Maximum Duty Factor for BGxxx		$V_{\text{FREQ}} = 0\text{V}$		93		%

INTV_{CC} Low Dropout (LDO) Linear Regulators

INTV _{CC} Voltage for V_{BIAS} and EXTV_{CC} LDOs		$\text{EXTV}_{CC} = 0\text{V}$ for V_{BIAS} LDO, $\text{EXTV}_{CC} = 12\text{V}$ for EXTV_{CC} LDO				
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(Specifications are at $T_J = -40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$ for the minimum and maximum values, $T_A = 25^{\circ}\text{C}$ for the typical values, $V_{BIAS} = 12\text{V}$, RUN1 and $\text{RUN2} = 5\text{V}$, $\text{VPRG1} = \text{Float}$, $\text{EXTV}_{CC} = 0\text{V}$, $\text{DRVSET} = 0\text{V}$, $\text{DRVUV} = 0\text{V}$, DTCA and $\text{DTCB} = 0\text{V}$, unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS/COMMENTS	MIN	TYP	MAX	UNITS
		$\text{DRVSET} = \text{INTV}_{CC}$	5.2	5.5	5.7	V
		$\text{DRVSET} = 0\text{V}$	4.8	5.0	5.2	V
		$\text{DRVSET} = 64.9\text{k}\Omega$	4.5	4.75	5.0	V
DRV_{CC} Load Regulation		DRV_{CC} load current = 0mA to 100mA, $T_A = 25^{\circ}\text{C}$		1	3	%
Undervoltage Lockout	UVLO	DRV_{CC} Rising				
		$\text{DRVUV} = \text{INTV}_{CC}$	4.8	5.0	5.2	V
		$\text{DRVUV} = 0\text{V}$	3.6	3.8	4.0	V
		$\text{DRVUV} = \text{floating}$	4.2	4.4	4.6	V
		DRV_{CC} Falling				
		$\text{DRVUV} = \text{INTV}_{CC}$	4.55	4.75	4.95	V
		$\text{DRVUV} = 0\text{V}$	3.4	3.6	3.8	V
EXTV_{CC} LDO Switchover Voltage EXTV_{CC} Rising		$\text{DRVUV} = \text{INTV}_{CC}$ or floating, $T_A = 25^{\circ}\text{C}$	5.75	5.95	6.15	V
		$\text{DRVUV} = 0\text{V}$, $T_A = 25^{\circ}\text{C}$	4.6	4.76	4.9	V
EXTV_{CC} LDO Switchover Hysteresis EXTV_{CC} Falling		$\text{DRVUV} = \text{INTV}_{CC}$ or floating		390		mV
		$\text{DRVUV} = 0\text{V}$		220		mV

Spread Spectrum Oscillator and Phase-Locked Loop (PLL)

Fixed Frequencies	f_{OSC}	$\text{PLLIN/SPREAD} = 0\text{V}$	320	370	420	kHz
		$\text{FREQ} = 0\text{V}$, $T_A = 25^{\circ}\text{C}$	2.0	2.25	2.5	MHz
		$\text{FREQ} = \text{INTV}_{CC}$		100		kHz
		$\text{FREQ} = 374\text{k}\Omega$				
		$\text{FREQ} = 75\text{k}\Omega$, $T_A = 25^{\circ}\text{C}$	450	500	550	kHz
Synchronizable Frequency Range	f_{SYNC}	$\text{PLLIN/SPREAD} = \text{External Clock}$	0.1		3	MHz
PLLIN Input High-Level			2.2			V
PLLIN Input Low-Level					0.5	V
Spread Spectrum Frequency Range (Relative to f_{OSC})		$\text{PLLIN/SPREAD} = \text{INTV}_{CC}$				
		Minimum Frequency		0		%
		Maximum Frequency		20		%

(Specifications are at $T_J = -40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$ for the minimum and maximum values, $T_A = 25^{\circ}\text{C}$ for the typical values, $V_{BIAS} = 12\text{V}$, RUN1 and $\text{RUN2} = 5\text{V}$, $\text{VPRG1} = \text{Float}$, $\text{EXTV}_{CC} = 0\text{V}$, $\text{DRVSET} = 0\text{V}$, $\text{DRVUV} = 0\text{V}$, DTCA and $\text{DTCB} = 0\text{V}$, unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS/COMMENTS	MIN	TYP	MAX	UNITS
PGOODx Outputs						
PGOODx Voltage Low		PGOODx = 2mA, $T_A = 25^{\circ}\text{C}$		0.2	0.4	V
PGOODx Leakage Current		PGOODx = 5V, $T_A = 25^{\circ}\text{C}$	-1	0	+1	μA
PGOODx Trip Level (V_{FBx} with respect to Set Regulated Voltage)		$T_A = 25^{\circ}\text{C}$				
		V_{FBx} Rising	7	10	13	%
		Hysteresis		1.6		%
		V_{FBx} Falling	-13	-10	-7	%
		Hysteresis		1.6		%
PGOODx Delay for Reporting a Fault				25		μs

- ¹ The LTC7892 is tested in a feedback loop that servos ITHx voltage (V_{ITHx}) to a specified voltage and measures the resultant feedback voltage (V_{FBx}).
- ² SENSE1+ bias current is reflected in the bias supply by the formula $I_{\text{VBIAS}} = I_{\text{SENSE1}^+} \times V_{\text{BIAS}} / (V_{\text{OUT1}} \times \eta)$, where η is the efficiency.
- ³ Rise and fall times are measured using 10% and 90% levels. Delay times are measured using 50% levels unless otherwise noted.
- ⁴ TGxxx falling to BGxxx rising and BGxxx falling to TGxxx rising delay times are measured at the rising and falling thresholds on TGxxx and BGxxx of approximately 1V. See [Figure 40](#) and [Figure 41](#) for more details.
- ⁵ The minimum on-time condition specified for inductor peak-to-peak ripple current is $>40\%$ of the maximum load current (I_{MAX}). See the [Minimum On-Time Considerations](#) for more details.

ABSOLUTE MAXIMUM RATINGS

$T_A = 25^\circ\text{C}$ unless otherwise specified.

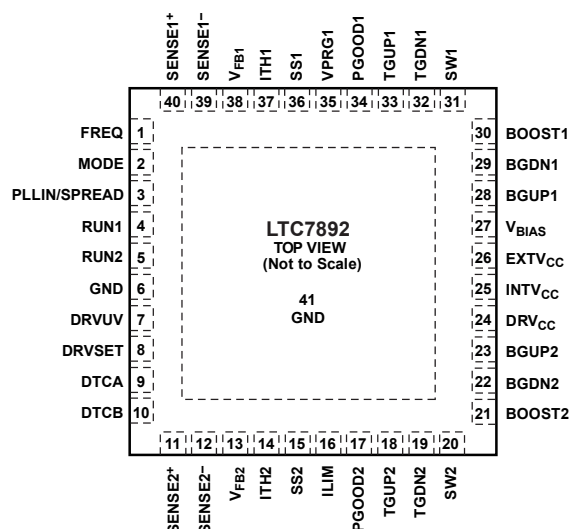
Table 2. Absolute Maximum Ratings

PARAMETER	RATING
Bias Input Supply (V_{BIAS})	-0.3V to 100V
RUN1 and RUN2	-0.3V to 100V
BOOST1 and BOOST2	-0.3V to 106V
SW1 and SW2	-5V to 100V
BOOST1 to SW1 and BOOST2 to SW2	-0.3V to 6V
TGUP1, TGUP2, TGDN1, TGDN2 ¹	Not applicable
BGUP1, BGUP2, BGDN1, BGDN2 ¹	Not applicable
EXTV _{CC}	-0.3V to 30V
DRV _{CC} and INTV _{CC}	-0.3V to 6V
V _{FB1}	-0.3V to 65V
PLLIN/SPREAD FREQ and V _{FB2}	-0.3V to 6V
SS1, SS2, ITH1, and ITH2	-0.3V to 6V
DRVSET and DRVUV	-0.3V to 6V
MODE, ILIM, and VPRG1	-0.3V to 6V
PGOOD1 and PGOOD2	-0.3V to 6V
DTCA and DTCB	-0.3V to 6V
SENSE1 ⁺ , SENSE2 ⁺ , SENSE1 ⁻ , and SENSE2 ⁻	-0.3V to 65V
SENSE1 ⁺ to SENSE1 ⁻ and SENSE2 ⁺ to SENSE2 ⁻ Continuous	-0.3V to +0.3V
SENSE1 ⁺ to SENSE1 ⁻ and SENSE2 ⁺ to SENSE2 ⁻ < 1ms	-100mA to +100mA
Operating Junction Temperature Range ²	-40°C to 125°C
Storage Temperature Range	-65°C to 150°C

¹ Do not apply a voltage or current source to these pins. They must be connected to capacitive loads only. Otherwise, permanent damage can occur.

² The LTC7892 is specified over the -40°C to 125°C operating junction temperature range. High junction temperatures degrade operating lifetimes. Note that the maximum ambient temperature consistent with these specifications is determined by specific operating conditions in conjunction with the board layout, rated package thermal impedance, and other environmental factors. The junction temperature (T_J , in °C) is calculated from the ambient temperature (T_A , in °C) and power dissipation (P_D , in Watts) according to the following formula: $T_J = T_A + (P_D \times \theta_{JA})$, where θ_{JA} is the package thermal impedance and equals 33°C/W for the 40-lead (6 mm × 6 mm), side wettable, quad flat no-lead (QFN) package.

PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS



NOTES
 1. THE EXPOSED PAD (PIN 41) MUST BE SOLDERED TO PCB GROUND FOR RATED ELECTRICAL AND THERMAL PERFORMANCE.

003

Figure 3. Pin Configuration

Table 3. Pin Descriptions

PIN	NAME	DESCRIPTION
1	FREQ	Frequency Control pin for the internal Voltage Controlled Oscillator (VCO). Connect FREQ to GND for a fixed frequency of 370kHz. Connect FREQ to INTV _{CC} for a fixed frequency of 2.25MHz. Program frequencies between 100kHz and 3MHz by using a resistor between FREQ and GND. Minimize the capacitance on FREQ.
2	MODE	Mode Select Input. This input determines how the LTC7892 operates at light loads. Connect MODE to GND to select Burst Mode® operation. An internal 100kΩ resistor to GND also invokes Burst Mode operation when MODE is floating. Connect MODE to INTV _{CC} to force continuous inductor current operation. Tying MODE to INTV _{CC} through a 100kΩ resistor selects the PS operation.
3	PLLIN/ SPREAD	External Synchronization Input to Phase Detector/Spread Spectrum Enable. When an external clock is applied to PLLIN/SPREAD, the PLL forces the rising BGxx1 signal to synchronize with the rising edge of the external clock. When not synchronizing to an external clock, tie this input to INTV _{CC} to enable spread spectrum dithering of the oscillator, or to GND to disable spread spectrum dithering.
4	RUN1	Run Control Input for Channel 1. Forcing RUN1 less than 1.08V disables controller switching. Forcing RUN1 and RUN2 less than 0.7V shuts down the LTC7892, reducing I _Q to approximately 1μA. Tie the RUN1 pin to V _{BIAS} to ensure it is always in operation.

5	RUN2	Run Control Input for Channel 2. Forcing RUN2 less than 1.08V disables controller switching. Forcing RUN1 and RUN2 less than 0.7V shuts down the LTC7892, reducing I_Q to approximately 1 μ A. Tie the RUN2 pin to V_{BIAS} to ensure it is always in operation.
6	GND	Ground. The GND pin and the exposed pad must be soldered to PCB ground for rated electrical and thermal performance.
7	DRVUV	DRV _{CC} UVLO and EXTV _{CC} Switchover Program Pin. DRVUV determines the INTV _{CC} UVLO and EXTV _{CC} switchover rising and falling thresholds, as listed in Table 1 .
8	DRVSET	INTV _{CC} Regulation Program Pin. DRVSET sets the regulation point for the INTV _{CC} LDO linear regulators. Connect DRVSET to GND to set INTV _{CC} to 5V. Connect DRVSET to INTV _{CC} to set INTV _{CC} to 5.5V. Program voltages between 4V and 5.5V by placing a resistor (43k Ω to 110k Ω) between DRVSET and GND. The resistor and an internal 20 μ A source current create a voltage used by the INTV _{CC} LDO regulator to set the regulation point.
9	DTCA	Dead Time Control Pin for Bottom FET Off to Top FET On Delay. Connect DTCA to GND to program an adaptive dead time delay of approximately 15ns. Connect a resistor between DTCA and GND to program a nonadaptive (open-loop) dead time delay from 7ns to 60ns.
10	DTCB	Dead Time Control Pin for Top FET Off to Bottom FET On Delay. Connect to GND to program an adaptive TG off to BG on a dead time delay of approximately 15ns. Connect a resistor between DTCB and GND to program a nonadaptive (open-loop) TG off to BG on dead time from 7ns to 60ns.
11	SENSE2 ⁺	Positive Input to the Differential Current Comparator for Channel 2. The SENSE2 ⁺ pin supplies current to the current comparator for Channel 2 when SENSE2 ⁺ is greater than INTV _{CC} .
12	SENSE2 ⁻	Negative Input to the Differential Current Comparator for Channel 2. The ITH2 pin voltage and controlled offset between the SENSE2 ⁺ and SENSE2 ⁻ pins, in conjunction with the current sense resistor (R_{SENSE}), set the current trip threshold.
13	V _{FB2}	Error Amplifier Feedback Input for Channel 2. V _{FB2} Receives the remotely sensed feedback voltage for channel 2 from an external resistive divider across the output. Tie V _{FB2} to INTV _{CC} for a 2-phase single output application, in which both channels share V _{FB1} , ITH1, and SS1.
14	ITH2	Error Amplifier Output and Switching Regulator Compensation Point for Channel 2. The current comparator trip point increases with this control voltage.
15	SS2	External Soft Start Input for Channel 2. SS2 regulates the V _{FB2} voltage to the lesser of 1.2V or the voltage on the SS2 pin. An internal 12 μ A pull-up current source is connected to SS2. A capacitor to GND at SS2 sets the ramp time to the final regulated output voltage. The ramp time is equal to 1ms for every 10nF of capacitance.
16	ILIM	Current Comparator Sense Voltage Range Input. Tying ILIM to GND or INTV _{CC} or floating it sets the maximum current sense threshold to one of three different levels (25mV, 75mV, and 50mV, respectively).
17	PGOOD2	Power Good Open-Drain Logic Output for Channel 2. PGOOD2 is pulled to the ground when the voltage on V _{FB2} is not within $\pm 10\%$ of its set point.

18	TGUP2	High Current Gate Driver Pull-Up for Top FET for Channel 2. TGUP2 pulls up to BOOST2. Tie TGUP2 directly to the top FET gate for maximum gate drive transition speed on the gate rising edge. A resistor can be tied between TGUP2 and the top FET gate to adjust the gate rising slew rate.
19	TGDN2	High Current Gate Driver Pull-Down for Top FET for Channel 2. TGDN2 pulls down to SW. Tie TGDN2 directly to the top FET gate for maximum gate drive transition speed on the gate falling edge. A resistor can be tied between TGDN2 and the top FET gate to adjust the gate falling slew rate.
20	SW2	Switch Node Connection to Inductor for Channel 2.
21	BOOST2	Bootstrapped Supply to the Top Side Floating Driver for Channel 2. Connect a capacitor between the BOOST2 and SW2 pins. An internal switch provides power to the BOOST2 pin from DRV _{CC} when the bottom FET turns on. The voltage swing at the BOOST2 pin is from DRV _{CC} to (V _{OUT2} + DRV _{CC}).
22	BGDN2	High Current Gate Driver Pull-Down for Bottom FET for Channel 2. BGDN2 pulls down to GND. Tie BGDN2 directly to the bottom FET gate for maximum gate drive transition speed on the gate falling edge. A resistor can be tied between BGDN2 and the bottom FET gate to adjust the gate falling slew rate. BGDN2 also serves as the Kelvin sense of the bottom FET gate during turn-on.
23	BGUP2	High Current Gate Driver Pull-Up for Bottom FET for Channel 2. BGUP2 pulls up to DRV _{CC} . Tie BGUP2 directly to the bottom FET gate for maximum gate drive transition speed on the gate rising edge. A resistor can be tied between BGUP2 and the bottom FET gate to adjust the gate falling slew rate. BGUP2 also serves as the Kelvin sense of the bottom FET gate during turn-off.
24	DRV _{CC}	Gate Driver Power Supply Pin. The gate drivers are powered from DRV _{CC} . Connect DRV _{CC} to INTV _{CC} by a separate trace to the INTV _{CC} bypass capacitor.
25	INTV _{CC}	Output of the Internal Low Dropout Regulator. The INTV _{CC} voltage regulation point is set by the DRVSET pin. INTV _{CC} must be decoupled to ground with a 4.7μF to 10μF ceramic or other low equivalent series resistance (ESR) capacitor.
26	EXTV _{CC}	External Power Input to an Internal LDO Connected to DRV _{CC} . This LDO supplies INTV _{CC} power, bypassing the internal V _{BIAS} LDO whenever EXTV _{CC} exceeds the EXTV _{CC} switchover voltage. See EXTV _{CC} Connection Power and Bias Supplies (V_{BIAS}, EXTV_{CC}, DRV_{CC}, INTV_{CC}) section. Do not exceed 30V on EXTV _{CC} . Connect EXTV _{CC} to the ground if the EXTV _{CC} LDO is not used.
27	V _{BIAS}	Main Supply Pin. A bypass capacitor should be tied between V _{BIAS} and GND.
28	BGUP1	High Current Gate Driver Pull-Up for Bottom FET for Channel 1. BGUP1 pulls up to DRV _{CC} . Tie BGUP1 directly to the bottom FET gate for maximum gate drive transition speed on the gate rising edge. A resistor can be tied between BGUP1 and the bottom FET gate to adjust the gate falling slew rate. BGUP1 also serves as the Kelvin sense of the bottom FET gate during turn-off.
29	BGDN1	High Current Gate Driver Pull-Down for Bottom FET for Channel 1. BGDN1 pulls down to GND. Tie BGDN1 directly to the bottom FET gate for maximum gate drive transition speed on the gate falling edge. A resistor can be tied between BGDN1 and the bottom

		FET gate to adjust the gate falling slew rate. BGDN1 also serves as the Kelvin sense of the bottom FET gate during turn-on.
30	BOOST1	Bootstrapped Supply to the Top Side Floating Driver for Channel 1. Connect a capacitor between the BOOST1 and SW1 pins. An internal switch provides power to the BOOST1 pin from DRV_{CC} when the bottom FET turns on. The voltage swing at the BOOST1 pin is from DRV_{CC} to $(V_{OUT1} + DRV_{CC})$.
31	SW1	Switch Node Connection to Inductor for Channel 1.
32	TGDN1	High Current Gate Driver Pull-Down for Top FET for Channel 1. TGDN1 pulls down to SW. Tie TGDN1 directly to the top FET gate for maximum gate drive transition speed on the gate falling edge. A resistor can be tied between TGDN1 and the top FET gate to adjust the gate falling slew rate.
33	TGUP1	High Current Gate Driver Pull-Up for Top FET for Channel 1. TGUP1 pulls up to BOOST1. Tie TGUP1 directly to the top FET gate for maximum gate drive transition speed on the gate rising edge. A resistor can be tied between TGUP1 and the top FET gate to adjust the gate rising slew rate.
34	PGOOD1	Power Good Open Drain Logic Output for Channel 1. PGOOD1 is pulled to ground when the voltage on V_{FB1} is not within $\pm 10\%$ of its set point.
35	VPRG1	Output Voltage Control Pin for Channel 1. VPRG1 sets the adjustable output mode for Channel 1 using external feedback resistors or fixed 28V/24V output mode. Floating VPRG1 programs the output from 1.2V to 100V with an external resistor divider, regulating V_{FB1} to 1.2V. Connect VPRG1 to $INTV_{CC}$ or GND to program the output to 28V or 24V, respectively, through an internal resistor divider on V_{FB1} .
36	SS1	External Soft Start Input for Channel 1. SS1 regulates the V_{FB1} voltage to the lesser of 1.2V or the voltage on the SS1 pin. An internal $12\mu A$ pull-up current source is connected to SS1. A capacitor to GND at SS1 sets the ramp time to the final regulated output voltage. The ramp time is equal to 1ms for every 10nF of capacitance.
37	ITH1	Error Amplifier Output and Switching Regulator Compensation Point for Channel 1. The current comparator trip point increases with this control voltage.
38	V_{FB1}	Error Amplifier Feedback Input for Channel 1. If the VPRG1 pin is floating, V_{FB1} receives the remotely sensed feedback voltage for Channel 1 from an external resistive divider across the output. If VPRG1 is tied to $INTV_{CC}$ or GND, the V_{FB1} pin receives the remotely sensed output voltage directly.
39	SENSE1 ⁻	Negative Input to the Differential Current Comparator for Channel 1. The ITH1 pin voltage and controlled offset between the SENSE1 ⁺ and SENSE1 ⁻ pins, in conjunction with the current sense resistor (R_{SENSE}), set the current trip threshold.
40	SENSE1 ⁺	Positive Input to the Differential Current Comparator for Channel 1. The SENSE1 ⁺ pin supplies current to the current comparator for Channel 1 when SENSE1 ⁺ is greater than $INTV_{CC}$.
41	GND (Exposed Pad)	Ground (Exposed Pad). The exposed pad must be soldered to PCB ground for rated electrical and thermal performance.

TYPICAL PERFORMANCE CHARACTERISTICS

$T_A = 25^\circ\text{C}$, unless otherwise noted.

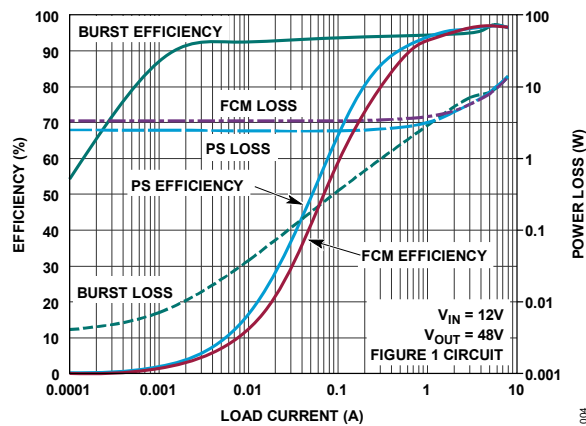


Figure 4. Efficiency and Power Loss vs Load Current

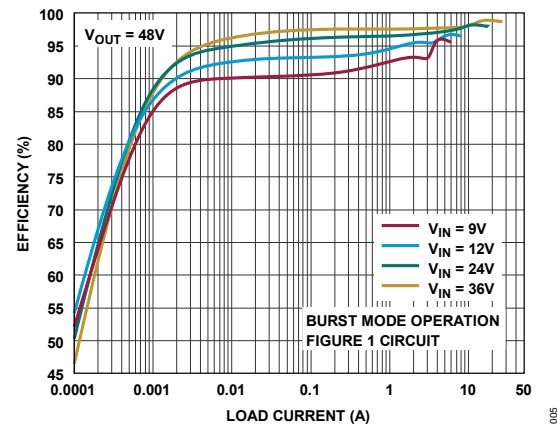


Figure 5. Efficiency vs Load Current

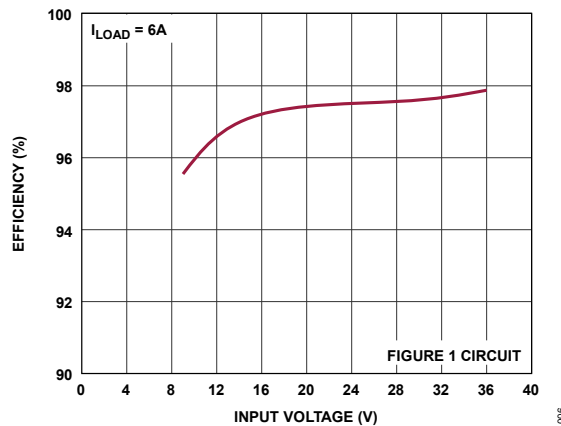


Figure 6. Efficiency vs Input Voltage

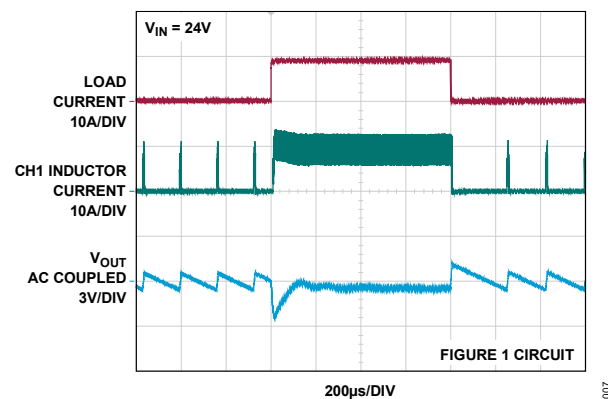


Figure 7. Load Step Burst Mode® Operation

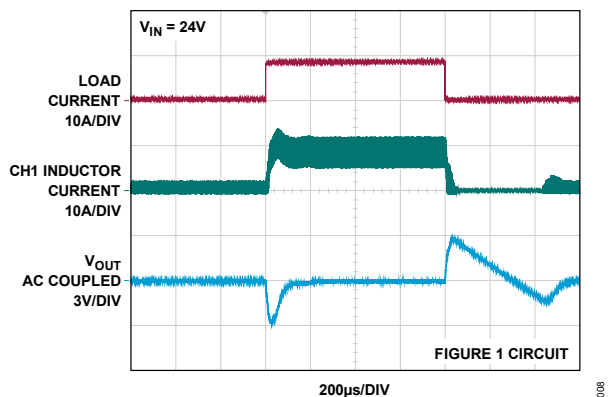


Figure 8. Load Step PS Mode

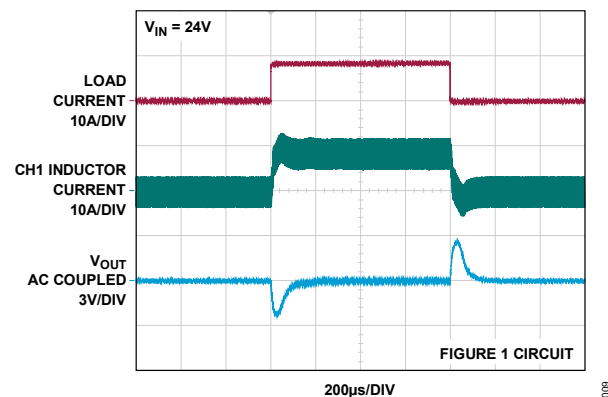


Figure 9. Load Step FCM

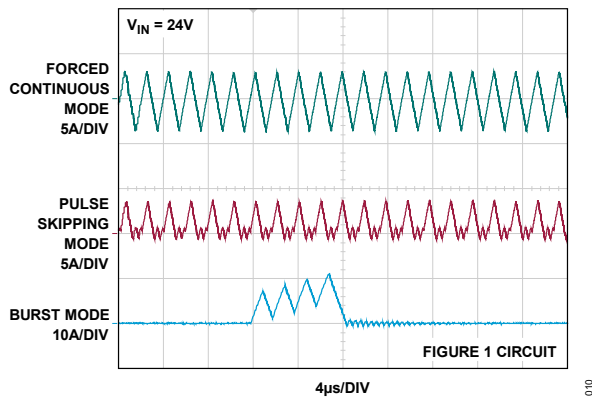


Figure 10. Inductor Current at Light Load

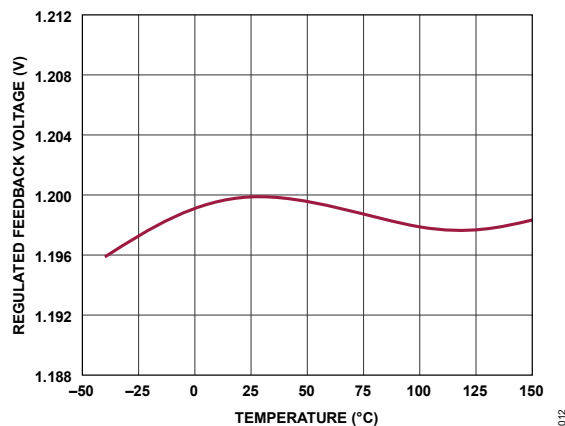


Figure 12. Regulated Feedback Voltage vs Temperature

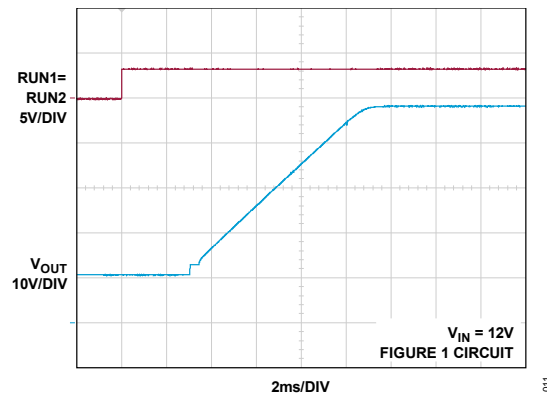
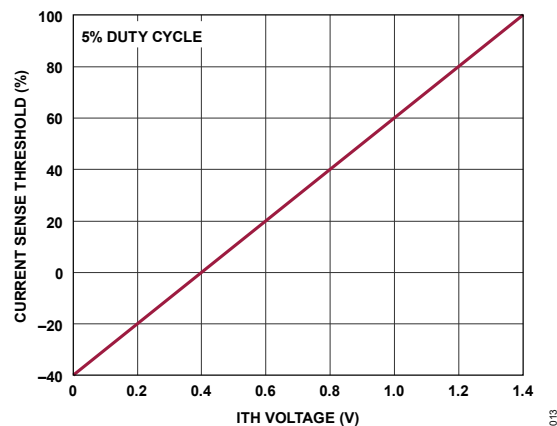
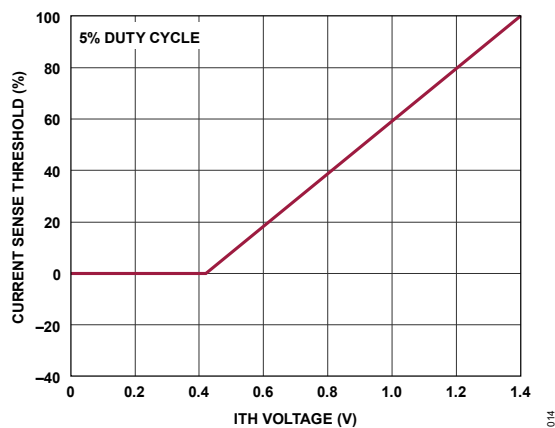
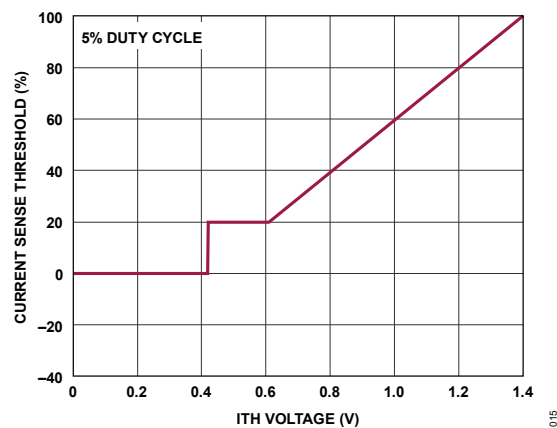


Figure 11. Soft Start-Up

Figure 13. Maximum Current Sense Threshold Relative to $V_{SENSE(MAX)}$ vs V_{ITHx} in FCMFigure 14. Maximum Current Sense Threshold Relative to $V_{SENSE(MAX)}$ vs V_{ITHx} Voltage in PS ModeFigure 15. Maximum Current Sense Threshold Relative to $V_{SENSE(MAX)}$ vs V_{ITHx} Voltage in Burst Mode

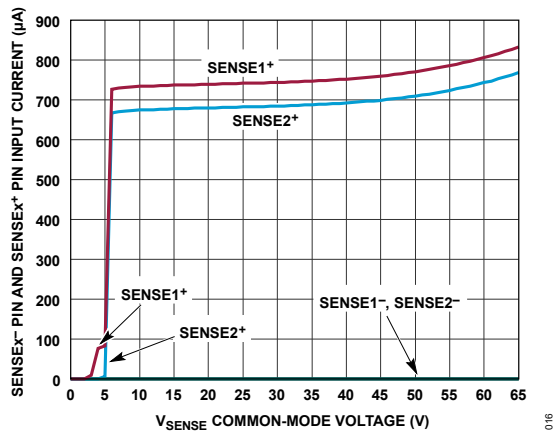


Figure 16. $SENSEx^+$ and $SENSEx$ Pin Input Bias Current vs V_{SENSE} Common-Mode Voltage

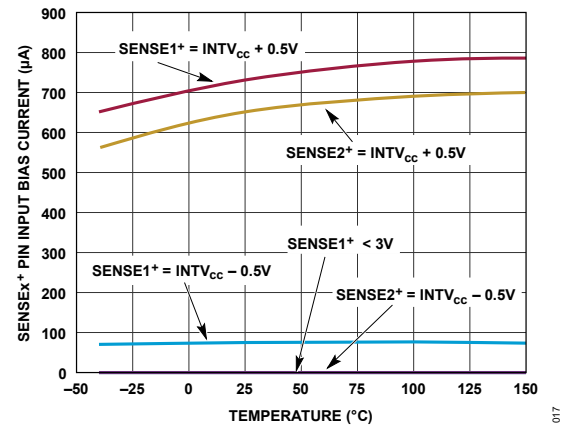


Figure 17. $SENSEx^-$ Pin Input Current vs. Temperature

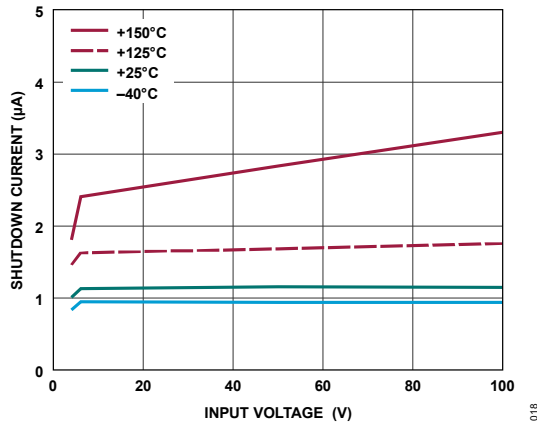


Figure 18. Shutdown Current vs. Input Voltage

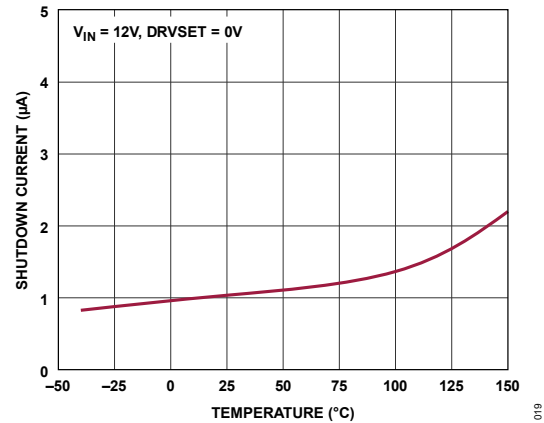


Figure 19. Shutdown Current vs Temperature

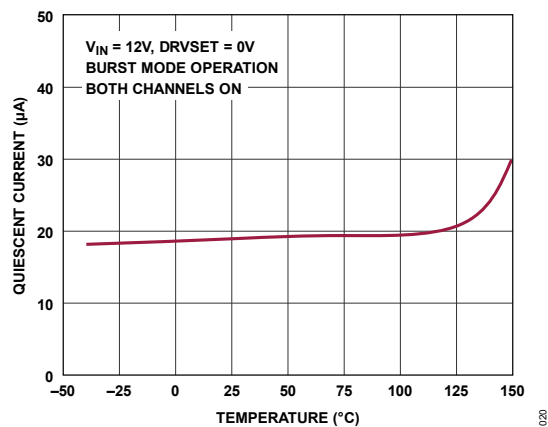


Figure 20. Quiescent Current vs Temperature

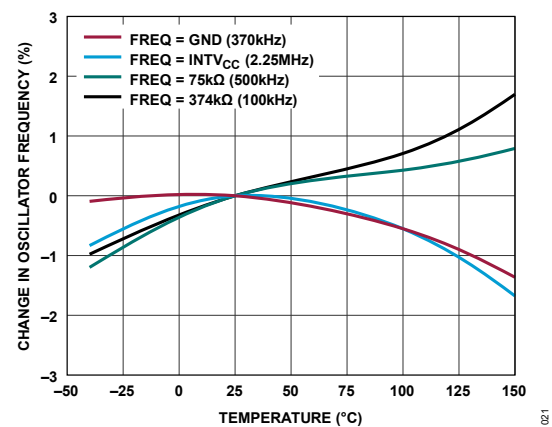


Figure 21. Oscillator Frequency vs. Temperature

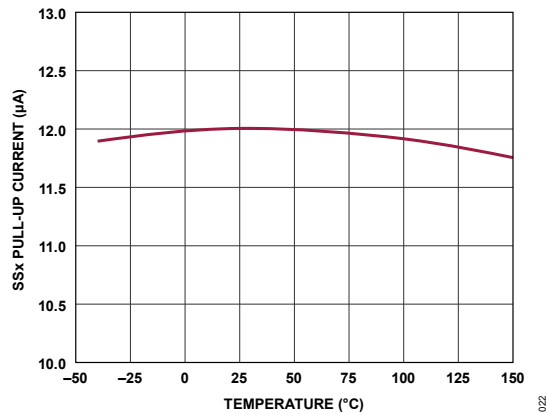


Figure 22. SSx Pull-Up Current vs. Temperature

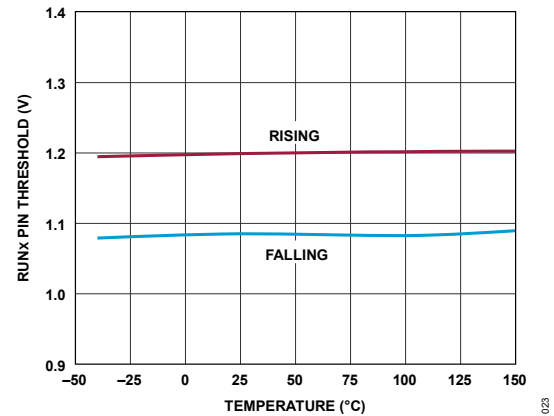


Figure 23. RUNx Pin Threshold vs. Temperature

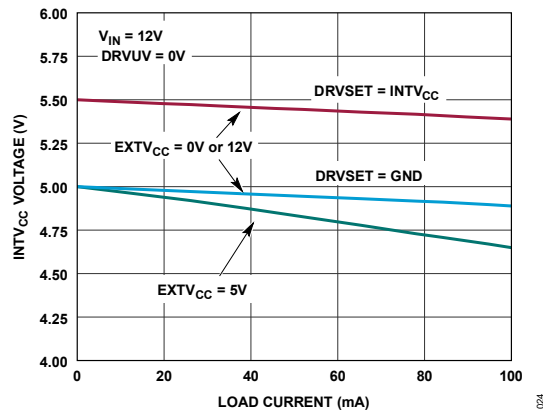


Figure 24. INTVcc Voltage vs. Load Current

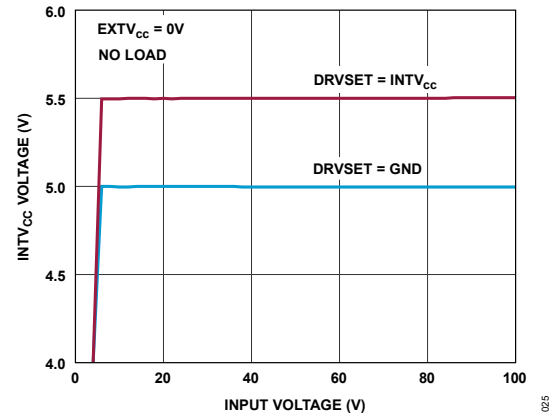


Figure 25. INTVcc Voltage vs. Input Voltage

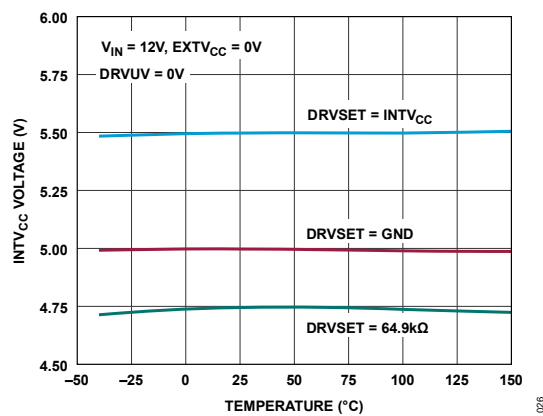


Figure 26. INTVcc Voltage vs. Temperature

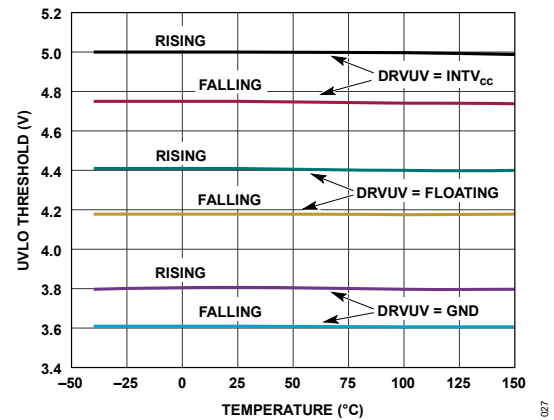


Figure 27. UVLO Threshold vs. Temperature

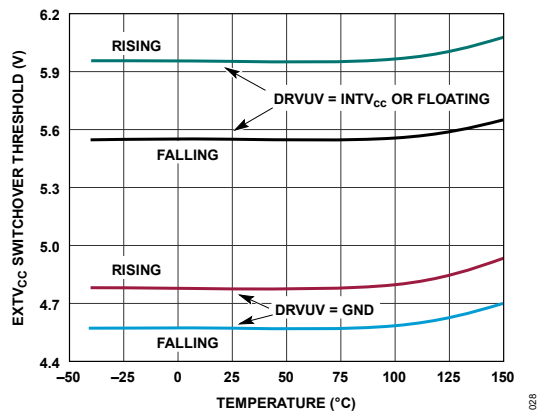
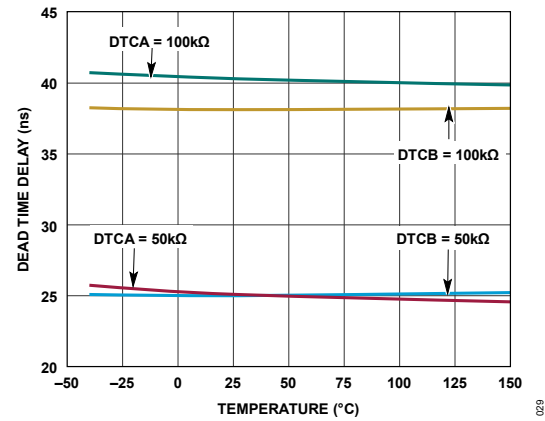
Figure 28. EXTV_{CC} Switchover Threshold vs. Temperature

Figure 29. Dead Time Delay vs. Temperature

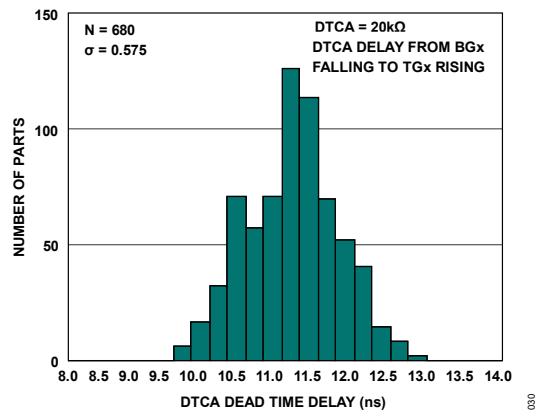


Figure 30. DTCA = 20kΩ Dead Time Delay Histogram

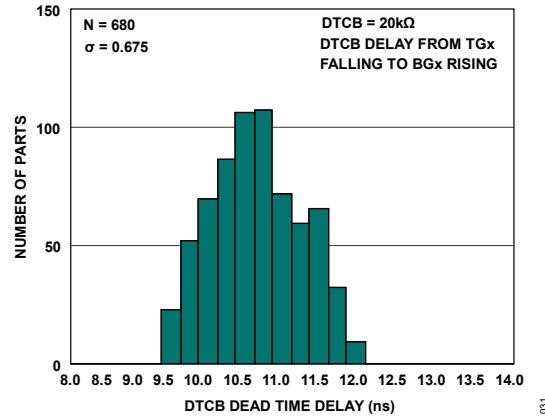


Figure 31. DTCB = 20kΩ Dead Time Delay Histogram

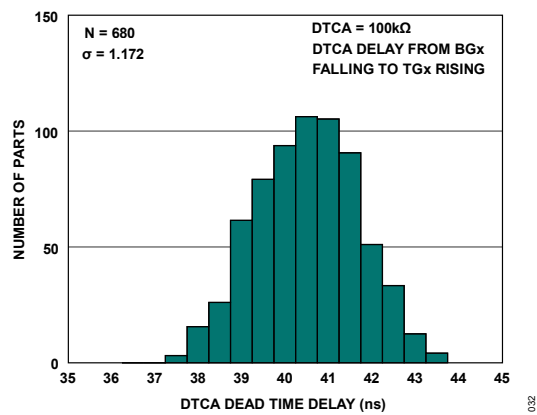


Figure 32. DTCA = 100kΩ Dead Time Delay Histogram

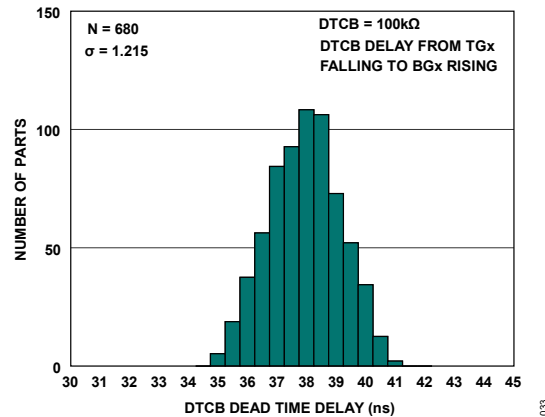


Figure 33. DTCB = 100kΩ Dead Time Delay Histogram

[illegible]

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THEORY OF OPERATION

Main Control Loop

The LTC7892 is a dual synchronous boost controller utilizing a constant frequency, peak current mode architecture. The two controller channels operate 180° out of phase, which reduces the required input capacitance and power supply-induced noise. During normal operation, the external bottom FET turns on when the clock sets the set/reset (SR) latch, causing the inductor current to increase. The main switch is turned off when the main current comparator, ICMP, resets the SR latch. After the bottom FET is turned off each cycle, the top FET is turned on, which causes the inductor current to decrease until either the inductor current starts to reverse, as indicated by the current comparator IR, or the beginning of the next clock cycle.

The peak inductor current at which ICMP trips and resets the latch is controlled by the voltage on the ITHx pin, which is the output of the error amplifier. The error amplifier compares the output voltage feedback signal at the V_{FBx} pin, (which is generated with an external resistor divider connected across the output voltage, V_{OUTx} , to GND) to the internal 1.2V reference voltage. When the load current increases, it causes a slight decrease in V_{FBx} relative to the reference, which causes the error amplifier to increase the ITHx voltage until the average inductor current matches the new load current.

Power and Bias Supplies (V_{BIAS} , $EXTV_{CC}$, DRV_{CC} , $INTV_{CC}$)

The $INTV_{CC}$ pin supplies power for the top and bottom FET drivers and most of the internal circuitry. The supply for the FET drivers is derived from the DRV_{CC} pin, which must be tied to the $INTV_{CC}$ pin to supply power to the gate drivers. LDOs (low dropout linear regulators) are available from the V_{BIAS} and $EXTV_{CC}$ pins to provide power to $INTV_{CC}$, which can be programmed from 4V to 5.5V through control of the $DRVSET$ pin. When the $EXTV_{CC}$ pin is tied to a voltage less than its switchover voltage, the V_{BIAS} LDO supplies power to $INTV_{CC}$. If $EXTV_{CC}$ is taken more than its switchover voltage, the V_{BIAS} LDO regulator turns off, and the $EXTV_{CC}$ LDO is turned on. When enabled, the $EXTV_{CC}$ LDO regulator supplies power to $INTV_{CC}$. Using the $EXTV_{CC}$ pin allows the $INTV_{CC}$ power to be derived from a high-efficiency external source.

High Side Bootstrap Capacitor

Each top FET driver is biased from the floating bootstrap capacitor C_B , which normally recharges through an internal switch between $BOOSTx$ and DRV_{CC} whenever the bottom FET turns on. The internal switch becomes high impedance whenever the bottom FET is off, which prevents the bootstrap capacitor from overcharging if SWx rings less than GND during the dead times.

If the input voltage increases to a voltage close to a voltage close to its output, the loop can enter dropout and attempt to turn on the top FET continuously. If the bottom FET is not turned on frequently enough to recharge the bootstrap capacitor, the top FET may not be fully enhanced, or it may even be completely off when the controller attempts to turn on the top FET.

Dead Time Control (DTCA and DTCB Pins)

The LTC7892 dead time delays can be programmed from 7ns to 60ns through the configuration of the DTCA and DTCB pins. The DTCA pin programs the dead time associated with the bottom FET turning off and the top FET turning on (SWx going from low to high). The DTCB pin programs the dead time associated with the top FET turning off and the bottom FET turning on (SWx going from high to low).

Tying the DTCA pin to ground programs adaptive dead time control, which means the driver logic waits for the bottom FET to turn off before turning on the top FET. Adaptive dead time control results in dead times of approximately 15ns between BGx falling to TGx rising. Placing a resistor between the DTCA pin and ground programs the open-loop delay between the bottom FET turning off and the top FET turning on. This delay can be programmed between 7ns and 60ns. See the [Dead Time Control \(DTCA and DTCB Pins\)](#) section for more information.

Tying the DTCB pin to ground programs adaptive dead time control, which means the driver logic waits for the top FET to turn off before turning on the bottom FET. Adaptive dead time control results in dead times of approximately 15ns between TGx falling to BGx rising. Placing a resistor between the DTCB pin and ground programs the open-loop delay between the top FET turning off and the bottom FET turning on. This delay can be programmed between 7ns and 60ns. See the [Dead Time Control \(DTCA and DTCB Pins\)](#) section for more information.

Start-Up and Shutdown (RUN and SS Pins)

The two channels of the LTC7892 can be independently shut down using the RUN1 and RUN2 pins. Pulling a RUNx pin below 1.1V shuts down the main control loop for that channel. Pulling both RUNx pins below 0.7V disables both controllers and most internal circuits, including the INTV_{CC} LDO regulators. In this shutdown state, the LTC7892 draws only 1μA of current from V_{BIAS}.

The RUNx pin needs to be externally pulled up or driven directly by logic. Each RUNx pin can tolerate up to 100V. See [Absolute Maximum Ratings](#) for more details. Therefore, the RUNx pin can be conveniently tied to V_{IN} or V_{BIAS} in always-on applications where one or both controllers are enabled continuously and never shut down. Additionally, a resistive divider from V_{IN} to a RUNx pin can be used to set a precise input undervoltage lockout so that the power supply does not operate below a user-adjustable level.

The start-up of each channel's output voltage V_{OUTx} is controlled by the voltage on the corresponding SSx pin. When the voltage on the SSx pin is less than the 1.2V internal reference voltage, the LTC7892 regulates the V_{FBx} voltage to the SSx pin voltage instead of the 1.2V reference voltage. This allows the SSx pin to be used as a soft-start which smoothly ramps the output voltage on start-up. An external capacitor from the SSx pin to GND is charged by an internal 12μA pull-up current, creating a voltage ramp on the SSx pin. As the SSx voltage rises linearly from 0V to 1.2V (and beyond), the output voltage V_{OUTx} rises smoothly to its final value.

Light Load Operation: Burst Mode Operation, Pulse-Skipping Mode, or Forced Continuous Mode (MODE Pin)

The LTC7892 can be set to enter high-efficiency Burst Mode operation, constant frequency PS mode, or forced continuous conduction mode at low load currents.

To select the Burst Mode operation, tie the MODE pin to GND. To select forced continuous operation, tie the MODE pin to INTV_{CC}. To select PS mode, tie the MODE pin to a DC voltage greater than 1.2V and less than INTV_{CC} – 1.3V. An internal 100kΩ resistor to ground invokes Burst Mode operation when the MODE pin is floating, and PS mode when the MODE pin is tied to INTV_{CC} through an external 100kΩ resistor.

When the controllers are enabled for Burst Mode operation, the minimum peak current in the inductor is set to approximately 25% of its maximum value, even though the voltage on the ITHx pin might indicate a lower value. If

the average inductor current is higher than the load current, the error amplifier will decrease the voltage on the ITHx pin. When the ITHx voltage drops below 0.425V, the internal sleep signal goes high (enabling sleep mode), and both external FETs are turned off. The ITHx pin is then disconnected from the output of the error amplifier and parked at 0.45V.

In sleep mode, much of the internal circuitry is turned off, reducing the quiescent current (I_Q) drawn by the LTC7892. If one channel is in sleep mode and the other channel is shut down, the LTC7892 draws only 15 μ A of I_Q . If both channels are in sleep mode, the LTC7892 draws only 20 μ A of I_Q .

In sleep mode, the load current is supplied by the output capacitor. As the output voltage decreases, the output of the error amplifier rises. When the output voltage drops enough, the ITHx pin is reconnected to the output of the error amplifier, the sleep signal goes low, and the controller resumes normal operation by turning on the bottom FET on the next cycle of the internal oscillator.

When a controller is enabled for Burst Mode operation, the inductor current is not allowed to reverse. The reverse current comparator (IR) turns off the top FET just before the inductor current reaches zero, preventing it from reversing and going negative. Thus, the controller operates in discontinuous operation.

In forced continuous operation, the inductor current is allowed to reverse at light loads or under large transient conditions. The peak inductor current is determined by the voltage on the ITHx pin, just as in normal operation. In this mode, the efficiency at light loads is lower than in the Burst Mode operation. However, continuous operation has the advantage of lower output voltage ripple and less interference to audio circuitry. In forced continuous mode, the output ripple is independent of the load current.

When the MODE pin is connected for pulse-skipping mode, the LTC7892 operates in pulse-width modulation (PWM) pulse-skipping mode at light loads. In this mode, constant frequency operation is maintained down to approximately 1% of the designed maximum output current. At very light loads, ICMP can remain tripped for several cycles and force the bottom FET to stay off for the same number of cycles (that is, skipping pulses). The inductor current is not allowed to reverse (discontinuous operation). This mode, like forced continuous operation, exhibits low output ripple as well as low audio noise and reduced RF interference as compared to Burst Mode operation. PS mode provides higher low current efficiency than FCM, but not nearly as high as Burst Mode operation.

Unlike FCM and pulse-skipping mode, Burst Mode cannot be synchronized to an external clock. Therefore, if Burst Mode operation is selected and the switching frequency is synchronized to an external clock applied to the PLLIN/SPREAD pin, the LTC7892 switches from Burst Mode to FCM.

Frequency Selection, Spread Spectrum, and Phase-Locked Loop (FREQ and PLLIN/SPREAD Pins)

The free-running switching frequency of the LTC7892 controller is selected using the FREQ pin. Tying FREQ to GND selects 370kHz, while tying FREQ to INTV_{CC} selects 2.25MHz. Placing a resistor between FREQ and GND allows the frequency to be programmed between 100kHz and 3MHz.

Switching regulators can be particularly troublesome for applications where electromagnetic interference (EMI) is a concern. To improve EMI, the LTC7892 can operate in spread spectrum mode, which is enabled by tying the PLLIN/SPREAD pin to INTV_{CC}. This feature varies the switching frequency within typical boundaries of the frequency set by the FREQ pin and +20%.

A PLL is available on the LTC7892 to synchronize the internal oscillator to an external clock source connected to the PLLIN/SPREAD pin. The PLL of the LTC7892 aligns the turn-on of the external bottom FET of Channel 1 to the rising

edge of the synchronizing signal. The turn-on of the external bottom FET for Channel 2 is 180° out-of-phase to the rising edge of the external clock source.

The PLL frequency is prebiased to the free running frequency set by the FREQ pin before the external clock is applied. If prebiased near the external clock frequency, the PLL only needs to make slight changes to synchronize the rising edge of the external clock to the rising edge of BG1. For a more rapid lock-in to the external clock, use the FREQ pin to set the internal oscillator to approximately the frequency of the external clock. The PLL of the LTC7892 is guaranteed to lock to an external clock source whose frequency is between 100kHz and 3MHz.

The PLLIN/SPREAD pin is Transistor-transistor logic (TTL) compatible with thresholds of 1.6V (rising) and 1.1V (falling) and is guaranteed to operate with a clock signal swing of 0.5V to 2.2V.

Output Overvoltage Protection

The LTC7892 has an overvoltage comparator for each channel that guards against transient overshoots and other more serious conditions that can cause output overvoltage. When the V_{FBx} pin rises more than 10% above its regulation point of 1.2V, the bottom FET is turned off, and the inductor current is not allowed to reverse.

Power Good

The LTC7892 has a PGOODx pin for each channel that is connected to an open drain of an internal N-channel MOSFET. The MOSFET turns on and pulls the PGOODx pin low when the V_{FBx} voltage is not within $\pm 10\%$ of the 1.2V reference. The PGOODx pin is also pulled low when the RUNx pin is low (shut down). When the V_{FBx} voltage is within the $\pm 10\%$ requirement, the MOSFET is turned off, and the PGOODx pin is allowed to be pulled up by an external resistor to a source no greater than 6V, such as $INTV_{CC}$.

When LTC7892 is operated in a 2-phase single output configuration, the output voltage is sensed by the V_{FB1} pin only. The PGOOD1 pin is pulled low when the V_{FB1} voltage is not within $\pm 10\%$ of the 1.2V reference. The PGOOD2 should be left floating.

APPLICATIONS INFORMATION

Figure 50 is a basic LTC7892 application circuit. External component selection is largely driven by the load requirement and begins with the selection of the inductor, current sense components, operating frequency, and light load operating mode. The remaining power stage components, consisting of the input and output capacitors, and power FETs can then be chosen. Next, feedback resistors are selected to set the desired output voltage. Then, the remaining external components are selected, such as for soft-start, biasing, and loop compensation.

Inductor Value Calculation

The operating frequency and inductor selection are interrelated in that higher operating frequencies allow the use of smaller inductor and capacitor values. A higher frequency generally results in lower efficiency because of FET switching and gate charge losses. In addition to this trade-off, the effect of inductor value on ripple current and low current operation must also be considered. The inductor value has a direct effect on the ripple current.

The maximum average inductor current ($I_{L(MAX)}$) in continuous conduction mode is equal to the maximum average output current ($I_{OUT(MAX)}$) multiplied by a factor of V_{OUT}/V_{IN} , or $I_{L(MAX)} = I_{OUT(MAX)} \cdot V_{OUT}/V_{IN}$. Be aware that the maximum output current decreases with decreasing V_{IN} . The choice of $I_{L(MAX)}$, therefore, depends on the maximum load current for a regulated V_{OUT} at the minimum normal operating V_{IN} . The choice of $I_{L(MAX)}$, therefore, depends on the maximum load current for a regulated V_{OUT} at the minimum normal operating V_{IN} . If the load current for a given V_{IN} is exceeded, V_{OUT} will decrease until the $I_{L(MAX)} = I_{OUT(MAX)} \cdot V_{OUT}/V_{IN}$ equation is satisfied.

The inductor ripple current (ΔI_L) for a boost converter is given by Equation 1:

$$\Delta I_L = \frac{1}{f \cdot L} V_{IN} \left(1 - \frac{V_{IN}}{V_{OUT}} \right) \quad (1)$$

Accepting larger values of ΔI_L allows the use of low inductances, but results in higher output voltage ripple and greater core losses. A reasonable starting point for setting ripple current is $\Delta I_L = 0.3 \cdot I_{L(MAX)}$. The maximum ΔI_L for a boost converter occurs at $V_{IN} = 1/2 V_{OUT}$.

The inductor value also has secondary effects. The transition to Burst Mode operation begins when the average inductor current required results in a peak current below 25% of the current limit determined by R_{SENSE} . Lower inductor values (higher ΔI_L) will cause this to occur at lower load currents, which can cause a dip in efficiency in the upper range of low-current operation. In the Burst Mode operation, lower inductance values will cause the burst frequency to decrease.

Inductor Core Selection

Once the value for L is known, the type of inductor must be selected. High-efficiency regulators generally cannot afford the core loss found in low-cost powdered iron cores, forcing the use of more expensive ferrite or molypermalloy cores. Actual core loss is independent of core size for a fixed inductor value, but it is very dependent on the inductance value selected. As inductance increases, core losses decrease. Unfortunately, increased inductance requires more turns of wire, and therefore, copper losses will increase.

Ferrite designs have a very low core loss and are preferred for high switching frequencies. Therefore, design goals can concentrate on copper loss and preventing saturation. Ferrite core material saturates hard, which means that inductance collapses abruptly when the peak design current is exceeded. This collapse results in an abrupt increase in inductor ripple current and consequent output voltage ripple. Do not allow the core to saturate.

Current Sense Selection

The LTC7892 can be configured to use either inductor DC resistance (DCR) sensing or low-value resistor sensing. The choice between the two current sensing schemes is a design trade-off between cost, power consumption, and accuracy. DCR sensing is popular because it saves expensive current sensing resistors and is more power efficient, particularly in high current applications. However, current sensing resistors provide the most accurate current limits for the controller. The selection of other external components begins with the selection of R_{SENSE} (if R_{SENSE} is used) and the inductor value.

The SENSEx⁺ and SENSEx⁻ pins are the inputs to the current comparator. The common-mode voltage range on these pins is 0V to 65V (see [Absolute Maximum Ratings](#) for more details), allowing the LTC7892 to operate from inputs over this full range. The SENSEx⁻ pins are high impedance, drawing less than $\approx 1\mu\text{A}$. This high impedance allows the current comparator to be used in inductor DCR sensing.

The impedance of the SENSEx⁺ pin changes depending on the common-mode voltage. When less than $\text{INTV}_{\text{CC}} - 0.5\text{V}$, the SENSEx⁺ pin is relatively high impedance, drawing $\approx 75\mu\text{A}$ for SENSE1⁺ and $\approx 1\mu\text{A}$ for SENSE2⁺. When the SENSEx⁺ pin is above $\text{INTV}_{\text{CC}} + 0.5\text{V}$, a higher current ($\approx 700\mu\text{A}$) flows into each pin. Between $\text{INTV}_{\text{CC}} - 0.5\text{V}$ and $\text{INTV}_{\text{CC}} + 0.5\text{V}$, the current transitions from the smaller current to the higher current. The SENSE1⁺ pin has an additional $\approx 75\mu\text{A}$ current when its voltage is above 3.2V to bias internal circuitry from V_{IN} instead of V_{BIAS} , which reduces the input referred supply current.

Filter components mutual to the sense lines must be placed close to the LTC7892, and the sense lines must run close together to a Kelvin connection underneath the current sense element, as shown in [Figure 35](#). Sensing current elsewhere can effectively add parasitic inductance and capacitance to the current sense element, degrading the information at the sense terminals and making the programmed current limit unpredictable. If DCR sensing is used (see [Figure 37](#)), the R1 resistor should be placed close to the switching node to prevent noise from coupling into sensitive small-signal nodes.

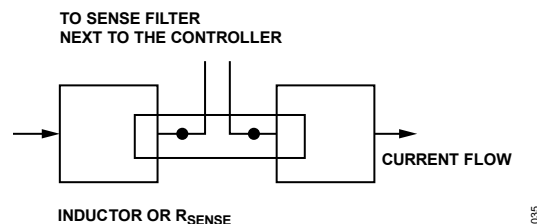


Figure 35. Sense Lines Placement with Inductor or Sense Resistor

Low Value Resistor Current Sensing

[Figure 36](#) shows a typical sensing circuit using a discrete resistor. R_{SENSE} is chosen based on the required output current. The current comparator has a maximum threshold $V_{\text{SENSE(MAX)}}$ of 50mV, 25mV, or 75mV, as determined by the state of the ILIM pin. The current comparator threshold voltage sets the peak inductor current.

Using the maximum inductor current ($I_{\text{L(MAX)}}$) and ripple current (ΔI_{L}) (as described in the [Inductor Value Calculation](#) section), the target sense resistor value is given by Equation 2, as follows:

$$R_{\text{SENSE}} = \frac{V_{\text{SENSE(MAX)}}}{I_{\text{L(MAX)}} + \frac{\Delta I_{\text{L}}}{2}} \quad (2)$$

To ensure that the application will deliver full load current over the full operating temperature range, choose the minimum value for $V_{\text{SENSE(MAX)}}$ as shown in [Table 1](#) (Electrical Characteristics table).

The parasitic inductance (ESL) of the sense resistor introduces significant error in the current sense signal for lower inductor value ($<3\mu\text{H}$) or higher current ($>5\text{A}$) applications. This error is proportional to the input voltage and can degrade line regulation or cause loop instability. Placing an RC filter (filter resistor, R_F and filter capacitor, C_F) into the SENSEx⁺ and SENSEx⁻ pins, as shown in [Figure 36](#), can be used to compensate for this error. For optimal cancellation of the ESL, set the RC filter time constant to $R_F \times C_F = \text{ESL}/R_{\text{SENSE}}$. In general, select C_F to be in the range of 1nF to 10nF and calculate the corresponding R_F . Surface-mount sense resistors in low ESL and wide footprint geometries are recommended to minimize this error. If not specified in the manufacturer's data sheet, the ESL can be approximated as 0.4nH for a resistor with a 1206 footprint and 0.2nH for a resistor with a 1225 footprint.

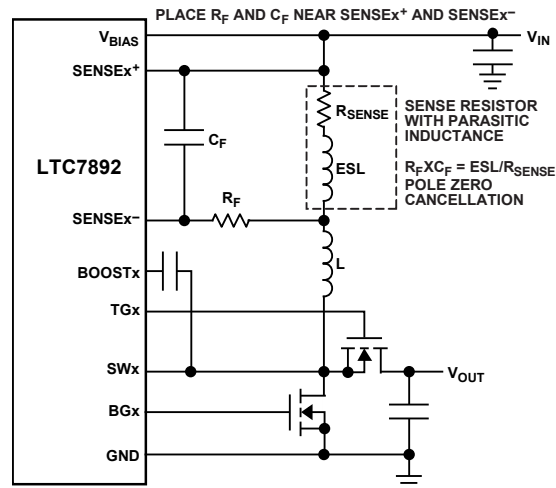


Figure 36. Using a Resistor to Sense Current

Inductor DCR Current Sensing

For applications requiring the highest possible efficiency at high load currents, the LTC7892 is capable of sensing the voltage drop across the inductor direct current resistance (DCR), as shown in [Figure 37](#). The DCR of the inductor represents the small amount of DC winding resistance of the copper, which can be less than 1mΩ for low-value, high-current inductors. In a high current application requiring such an inductor, power loss through a sense resistor would cost several points of efficiency compared to inductor DCR sensing.

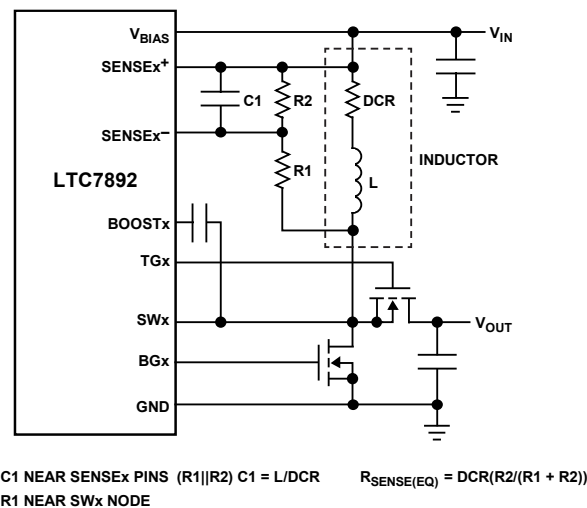


Figure 37. Using the Inductor DCR to Sense Current ($R_{\text{SENSE(EQ)}}$ is the Equivalent Sensed Resistance)

If the external $(R1 \parallel R2) \cdot C1$ time constant is chosen to be exactly equal to the L/DCR time constant, the voltage drop across the external capacitor is equal to the drop across the inductor DCR multiplied by $R2/(R1+R2)$. $R2$ scales the voltage across the sense terminals for applications where the DCR is greater than the target sense resistor value. To properly dimension the external filter components, the DCR of the inductor must be known. It can be measured using an inductance, capacitance, and resistance (LCR) meter, but the DCR tolerance is not always the same and varies with temperature. Refer to the manufacturer's data sheets for detailed information.

Using $I_{L(MAX)}$ and ΔI_L (as described in the [Inductor Value Calculation](#) section), the target sense resistor value is given by Equation 3 as follows:

$$R_{SENSE(EQUIV)} = \frac{V_{SENSE(MAX)}}{I_{L(MAX)} + \frac{\Delta I_L}{2}} \quad (3)$$

To ensure the application will deliver full load current over the full operating temperature range, choose the minimum value for $V_{SENSE(MAX)}$ in [Table 1](#) (Electrical Characteristics table).

Next, determine the DCR of the inductor. When provided, use the maximum value noted by the manufacturer, typically given at 20°C. Increase this value to account for the temperature coefficient of copper resistance, which is approximately 0.4%/°C. A conservative value for inductor temperature ($T_{L(MAX)}$) is 100°C. To scale the maximum inductor DCR (DCR_{MAX}) to the desired sense resistor value (R_D), use the divider ratio given by Equation 4, as follows:

$$R_D = \frac{R_{SENSE(EQUIV)}}{DCR_{MAX} \text{ at } T_{L(MAX)}} \quad (4)$$

$C1$ is typically selected to be in the range of 0.1μF to 0.47μF. This range forces the equivalent resistance ($R1 \parallel R2$) to around 2kΩ, reducing the error resulting from the ≈1μA current of the SENSE⁻ pin.

$R1 \parallel R2$ is scaled to the room temperature inductance, and the maximum DCR is given by Equation 5 as follows:

$$R1 \parallel R2 = \frac{L}{(DCR \text{ at } 20^\circ\text{C}) \cdot C1} \quad (5)$$

The sense resistor values are given by Equation 6 and Equation 7 as follows:

$$R1 = \frac{R1 \parallel R2}{R_D} \quad (6)$$

$$R2 = \frac{R1 \cdot R_D}{1 - R_D} \quad (7)$$

The maximum power loss (P_{LOSS}) in $R1$ is related to the duty cycle and occurs in continuous mode at $V_{IN} = 1/2 V_{OUT}$ given by Equation 8, as follows:

$$P_{LOSS} \text{ in } R1 = \frac{(V_{OUT} - V_{IN}) \cdot V_{IN}}{R1} \quad (8)$$

Ensure that $R1$ has a power rating higher than P_{LOSS} in $R1$. If high efficiency is necessary at light loads, consider this power loss when deciding whether to use DCR sensing or sense resistors. Light load power loss can be modestly higher with a DCR network than with a sense resistor, due to the extra switching losses incurred through $R1$. However, DCR sensing eliminates a sense resistor, reduces conduction losses, and provides higher efficiency at heavy loads. Peak efficiency is about the same with either method.

Setting the Operating Frequency

Selecting the operating frequency is a trade-off between efficiency and component size. High-frequency operation allows the use of smaller inductor and capacitor values. Operation at lower frequencies improves efficiency by reducing gate charge and transition losses but requires larger inductance values and/or more output capacitance to maintain low output ripple voltage.

In higher voltage applications, transition losses contribute more significantly to power loss, and a proper balance between size and efficiency is achieved with a switching frequency between 300kHz and 900kHz. Lower voltage applications benefit from lower switching losses and can operate at switching frequencies up to 3MHz, if desired. The switching frequency is set using the FREQ and PLLIN/SPREAD pins, as shown in [Table 4](#).

Table 4. Setting the Switching Frequency using FREQ and PLLIN/SPREAD

FREQ PIN	PLLIN/SPREAD PIN	FREQUENCY
0V	0V	370kHz
INTV _{CC}	0V	2.25MHz
Resistor to GND	0V	100kHz to 3MHz
Any of the Above	External Clock 100kHz to 3MHz	Phase-Locked to External Clock
Any of the Above	INTV _{CC}	Spread Spectrum f _{OSC} modulated 0% to +20%

Tying the FREQ pin to the ground selects 370kHz, whereas tying FREQ to INTV_{CC} selects 2.25MHz. Placing a resistor between FREQ and the ground allows the frequency to be programmed anywhere between 100kHz and 3MHz. Choose a FREQ pin resistor (R_{FREQ}) from [Figure 38](#) or Equation 9, as follows:

$$R_{\text{FREQ}}(\text{in k}\Omega) = \frac{37\text{MHz}}{f_{\text{osc}}} \quad (9)$$

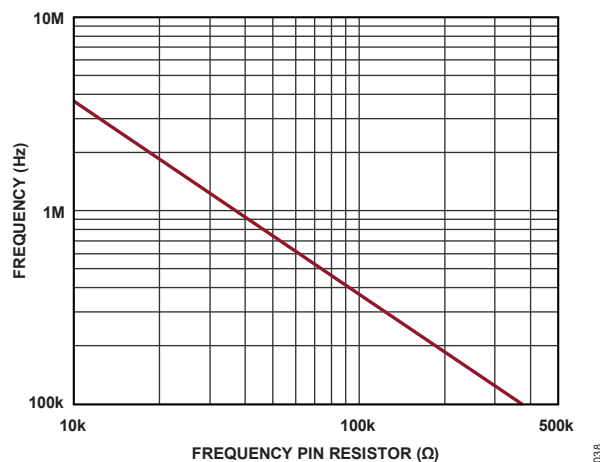


Figure 38. Relationship between Oscillator Frequency and Resistor Value at the FREQ Pin

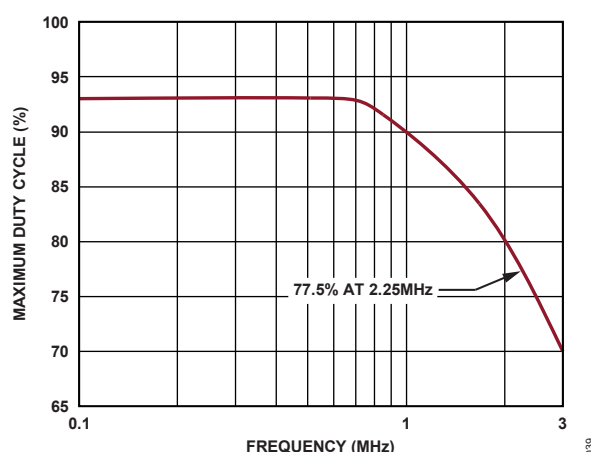


Figure 39. Relationship between Maximum Duty Cycle and Operating Frequency

A further constraint on the operating frequency is the maximum duty cycle of the boost converter. The maximum duty cycle (DC_{MAX}) is limited, as shown in [Figure 39](#), and can be approximated as $DC_{MAX} = (1 - V_{IN(MIN)}/V_{OUT}) \cdot 100\%$. If the duty cycle is greater than DC_{MAX} , the output can lose regulation and may not maintain the constant frequency operation. An operation frequency should be selected so that the boost converter duty cycle is less than DC_{MAX} .

To improve EMI performance, spread spectrum mode can optionally be selected by tying the PLLIN/SPREAD pin to $INTV_{CC}$. When the spread spectrum mode is enabled, the switching frequency modulates within the frequency selected by the FREQ pin and is +20%. Spread spectrum mode may be used in any operating mode selected by the MODE pin (Burst Mode, PS mode, or FCM).

A PLL is also available on the LTC7892 to synchronize the internal oscillator to an external clock source connected to the PLLIN/SPREAD pin. After the PLL locks, the BGxx1 is synchronized to the rising edge of the external clock signal, and BGxx2 is 180° out of phase from BGxx1. See the [Phase-Locked Loop and Frequency Synchronization](#) section for more details.

Selecting the Light-Load Operating Mode

The LTC7892 can be set to enter high-efficiency Burst Mode operation, constant frequency PS mode, or forced continuous conduction mode at light load currents. To select the Burst Mode operation, tie the MODE pin to GND. To select forced continuous operation, tie the MODE pin to $INTV_{CC}$. To select PS mode, tie the MODE pin to $INTV_{CC}$ through a 100kΩ resistor. An internal 100kΩ resistor from the MODE pin to the ground selects Burst Mode if the pin is floating. When synchronized to an external clock through the PLLIN/SPREAD pin, the LTC7892 operates in PS mode if it is selected. Otherwise, the LTC7892 operates in FCM. [Table 5](#) summarizes the use of the MODE pin to select the light load operating mode.

Table 5. Using the MODE Pin to Select Light Load Operating Mode

MODE PIN	LIGHT-LOAD OPERATING MODE	MODE WHEN SYNCHRONIZED
0V or Floating	Burst Mode	FCM
100kΩ to $INTV_{CC}$	PS Mode	PS Mode
$INTV_{CC}$	FCM	FCM

The requirements of each application dictate the appropriate choice for light load operating mode. In Burst Mode operation, the inductor current is not allowed to reverse. The reverse current comparator turns off the top FET just before the inductor current reaches zero, preventing it from reversing and going negative. Therefore, the regulator operates in discontinuous operation. In addition, when the load current is light, the inductor current begins bursting at frequencies lower than the switching frequency and enters a low-current sleep mode when not switching. As a result, Burst Mode operation has the highest possible efficiency at light load.

In FCM, the inductor current is allowed to reverse at light loads and switches at the same frequency regardless of load. In this mode, the efficiency at light loads is considerably lower than in the Burst Mode operation. However, continuous operation has the advantage of lower output voltage ripple and less interference to audio circuitry. In FCM, the output ripple is independent of the load current.

In PS mode, constant frequency operation is maintained down to approximately 1% of the designed maximum output current. At very light loads, the PWM comparator may remain tripped for several cycles and force the bottom FET to remain off for the same number of cycles (that is, skipping pulses). The inductor current is not allowed to reverse (discontinuous operation). This mode, like forced continuous operation, exhibits low output ripple as well as low audio noise and reduced RF interference as compared to Burst Mode operation. PS mode provides higher light load efficiency than FCM, but not nearly as high as Burst Mode operation. Consequently, PS mode represents a compromise between light load efficiency, output ripple, and EMI.

In some applications, it can be desirable to change the light load operating mode based on the conditions present in the system. For example, if a system is inactive, one might select high-efficiency Burst Mode operation by keeping the MODE pin set to 0V. When the system wakes, the user can send an external clock to PLLIN/SPREAD, or tie MODE to INTV_{CC} to switch to low noise forced continuous mode. These types of changes can allow an individual application to benefit from the advantages of each light load operating mode.

Dead Time Control (DTCA and DTCB Pins)

The dead time delays of the LTC7892 can be adjusted from 7ns to 60ns through configuration of the DTCA and DTCB pins. Refer to the timing diagrams on [Figure 40](#) and [Figure 41](#) show the TGx minus SWx and BGx waveforms for each DTCx pin setting. In the [DTCx Pin Tied to Ground \(Adaptive Dead Time Control\)](#) and [DTCx Pin connected with a resistor to GND](#) sections, TGx represents the voltage sensed at the top FET gate (the threshold for the TGx falling is sensed at the TGUPx pin), and BGx represents the voltage sensed at the bottom FET (the thresholds for the BGx rising and falling are sensed at the BGDNx and BGUPx pins respectively). The DTCA pin programs the dead time associated with the bottom FET turning off and the top FET turning on (SWx transitioning low to high). The DTCB pin programs the dead time associated with top FET turning off and the bottom FET turning on (SWx transitioning high to low).

DTCx Pin Tied to Ground (Adaptive Dead Time Control)

Tying the DTCA and DTCB pins to the GND program adaptive dead time control. In adaptive control (see [Figure 40](#)), the dead time is measured between one FET turning off and the other FET turning on. Tying the DTCA pin to GND fixes the delay between BGx falling and TGx minus SWx rising to approximately 15ns. Tying the DTCB pin to GND fixes the delay between TGx minus SWx falling and BGx rising to approximately 15ns.

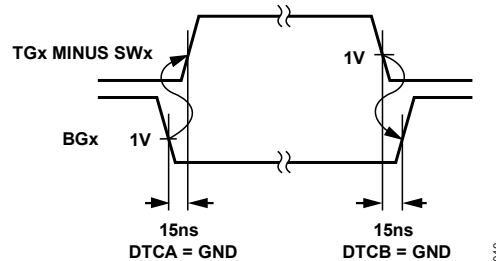


Figure 40. DTC Pin tied to GND – Adaptive Dead Time Control

DTCx Pin connected with a resistor to GND

Connecting a resistor between the DTCx pin and GND programs an open-loop dead time delay from 7ns to 60ns between the TGx minus SWx and BGx edges (see [Figure 41](#)). A resistor tied to the DTCA pin programs an open loop delay between BGx falling and TGx minus SWx rising. A resistor tied to the DTCB pin and GND programs an open loop delay between TGx minus SWx falling and BGx rising. [Figure 42](#) shows the relationship between the DTCx pin resistor value and the programmed delay between TGx minus SWx and BGx edges. This resistor must not be less than 10kΩ or more than 200kΩ.

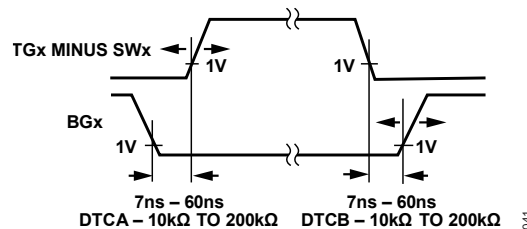


Figure 41. DTCx Pin with Resistor to GND – Adjustable Dead Time Control

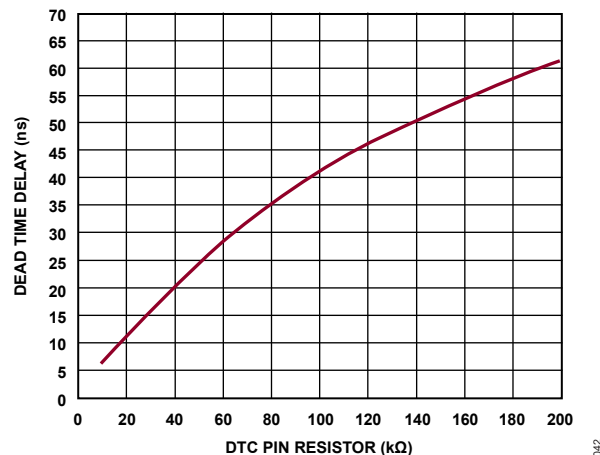


Figure 42. Relationship between Dead Time Delay and Resistor Value at the DTCx Pin

If one of the DTCx pins is programmed with a resistor, the other DTCx pin must be programmed with a resistor for proper dead time control operation. Unexpected dead time delays can result if one DTCx pin is programmed with a resistor while the other DTCx pin is tied to GND. The DTCx pins should only be connected to GND or a resistor tied to GND.

Power FET Selection

Two external power FETs must be selected for each controller in the LTC7892: one N-channel FET for the bottom (main) switch and one N-channel FET for the top (synchronous) switch. The peak-to-peak gate drive levels are set by the INTVCC regulation point (4V to 5.5V). Most GaN FETs can be driven comfortably within this INTVCC regulation window. If using silicon MOSFETs, logic-level threshold MOSFETs must be used in most applications. Pay close attention to the BVD_{SS} specification for the FETs as well.

Selection criteria for the power FETs include the on resistance ($R_{DS(ON)}$), Miller capacitance (C_{MILLER}), input voltage, and maximum output current. C_{MILLER} can be approximated from the gate charge curve typically provided in the datasheet of the FET manufacturer. C_{MILLER} is equal to the increase in gate charge along the horizontal axis, while the curve is approximately flat, divided by the specified change in the voltage difference between the drain and source terminals of the FET (V_{DS}). This result is then multiplied by the ratio of the application applied V_{DS} to the gate charge curve specified V_{DS} . When the IC is operating in continuous mode, the duty cycles for the top and bottom FETs are given by Equation 10 and Equation 11, as follows:

$$\text{Main Switch Duty Cycle} = \frac{V_{OUT} - V_{IN}}{V_{OUT}} \quad (10)$$

$$\text{Synchronous Switch Duty Cycle} = \frac{V_{IN}}{V_{OUT}} \quad (11)$$

The FET power dissipation at maximum output current is given by Equation 12 and Equation 13, as follows:

$$P_{MAIN} = \frac{(V_{OUT} - V_{IN})V_{OUT}}{V_{IN}^2} (I_{OUT(MAX)})^2 \cdot (1 + \delta)R_{DS(ON)} + \left(\frac{V_{OUT}^3}{V_{IN}} \right) \left(\frac{I_{OUT(MAX)}}{2} \right) \cdot (R_{DR})(C_{MILLER}) \cdot \left[\frac{1}{V_{INTVCC} - V_{THMIN}} + \frac{1}{V_{THMIN}} \right] (f) \quad (12)$$

$$P_{SYNC} = \frac{V_{OUT}}{V_{IN}} (I_{OUT(MAX)})^2 (1 + \delta)R_{DS(ON)} \quad (13)$$

where:

P_{MAIN} is the power dissipation from the main switch

δ is the temperature dependency of $R_{DS(ON)}$ ($\delta \approx 0.005/^{\circ}\text{C}$).

R_{DR} is the effective driver resistance at the FET's Miller threshold voltage ($R_{DR} \approx 2\Omega$).

V_{INTVCC} is the INTVCC voltage.

V_{THMIN} is the typical FET minimum threshold voltage.

P_{SYNC} is the power dissipation from the synchronous switch.

Both FETs have I^2R losses (I^2R is the power loss equation of the FETs when on in steady state), whereas the main N-channel equations include an additional term for transition losses, which are highest at low input voltages. For high input voltages, the high current efficiency generally improves with larger FETs. However, for low input voltages, the transition losses rapidly increase to the point that using a higher $R_{DS(ON)}$ device with lower C_{MILLER} provides higher efficiency. The synchronous FET losses are greatest at high input voltages when the bottom switch duty factor is low.

C_{IN} and C_{OUT} Selection

The input ripple current in a boost converter is relatively low (compared to the output ripple current) because the input current is continuous. The boost converter input capacitor (C_{IN}) voltage rating should exceed the maximum input voltage. Although ceramic capacitors are tolerant of overvoltage conditions, aluminum electrolytic capacitors are not. Be sure to characterize the input voltage for any possible overvoltage transients that could apply excess stress to the input capacitors.

The value of C_{IN} is a function of the source impedance, and in general, the higher the source impedance, the higher the required input capacitance. The required amount of input capacitance is also greatly affected by the duty cycle. High-output current applications that also experience high-duty cycles can place great demands on the input supply, both in terms of DC current and ripple current.

The selection of the output capacitance (C_{OUT}) is driven by the output voltage ripple (V_{RIPPLE}) requirement. The output current in a boost converter is discontinuous. Therefore, both the effects of ESR and the bulk capacitance must be considered when choosing C_{OUT}. V_{RIPPLE} due to charging and discharging the bulk capacitance of C_{OUT} is given by Equation 14, as follows:

$$V_{\text{RIPPLE}} = \frac{I_{\text{OUT(MAX)}} \cdot (V_{\text{OUT}} - V_{\text{IN(MIN)}})}{C_{\text{OUT}} \cdot V_{\text{OUT}} \cdot f} \quad (14)$$

The ripple due to the voltage drop across the ESR (ΔV_{ESR}) for C_{OUT} is given by Equation 12, as follows:

$$\Delta V_{\text{ESR}} = \left(I_{\text{L(MAX)}} + \frac{1}{2} \Delta I_{\text{L}} \right) \cdot \text{ESR} \quad (15)$$

Where:

ΔI_L is the ripple current in the inductor.

I_{L(MAX)} is the maximum average inductor current.

I_{OUT(MAX)} is the maximum average output current.

f is the operating frequency.

Multiple capacitors placed in parallel may be needed to meet the ESR and RMS current handling requirements. Dry tantalum, special polymer, aluminum electrolytic, and ceramic capacitors are all available in surface mount packages. Ceramic capacitors have excellent low ESR characteristics but can have a high voltage coefficient. Low ESR and high ripple current-rated capacitors such as OS-CON and POSCAP are available.

Single Output 2-Phase Operation

For high-power applications, the two channels can be operated in a 2-phase single output configuration. With 2-phase operation, the two channels are operated 180° out-of-phase which effectively interleaves the output current pulses. The interleaved current pulses double the maximum output current while reducing the output capacitor ripple current. The reduction in output capacitor ripple current lowers the capacitance and ESR requirements of the high-frequency output capacitor for a given output ripple voltage requirement.

The ripple current requirements for the output capacitor shown in Equation 14 can be reduced in a 2-phase configuration, as shown in [Figure 43](#). [Figure 43](#) illustrates the normalized output capacitor ripple current as a function of the duty cycle in a 2-phase configuration compared to a single-phase configuration. To choose a ripple current rating for the output capacitor in a 2-phase configuration, use the following steps:

1. Calculate the duty cycle range based on the output voltage and range of input voltage.
2. As shown in [Figure 43](#), choose the worst-case high normalized ripple current as a percentage of the maximum load current.

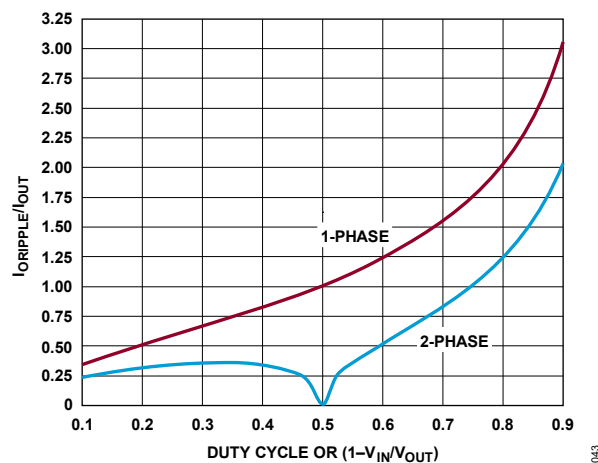


Figure 43. Normalized Output Capacitor Ripple Current (RMS) for a Boost Converter

To configure the LTC7892 for 2-phase operation, tie V_{FB2} to $INTV_{CC}$, $ITH2$ to ground, $SS2$ to ground, $PGOOD2$ to ground (or left floating), and $RUN2$ to $RUN1$.

The $RUN1$, V_{FB1} , $ITH1$, and $SS1$ pins are then used to control both channels, but each channel uses its own $ICMP$ and IR comparators to monitor their respective inductor currents.

[Figure 44](#) shows the configuration for a single output 2-phase operation and [Figure 50](#) shows a typical application configured for a single output 2-phase operation.

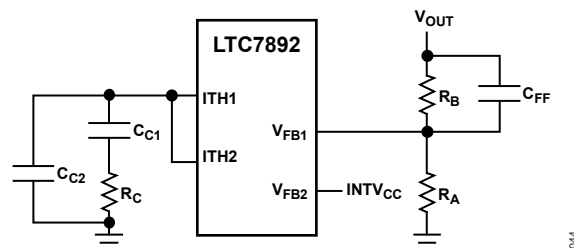


Figure 44. Configuration for Single Output 2-Phase Operation

Setting the Output Voltage

The LTC7892 output voltages are each set by an external feedback resistor divider carefully placed across the output, as shown in [Figure 45](#) and [Figure 46](#). The regulated output voltage is determined by Equation 16, as follows:

$$V_{OUT} = 1.2V(1 + \frac{R_B}{R_A}) \quad (16)$$

Place the R_A and R_B resistors close to the V_{FBx} pin to minimize printed circuit board (PCB) trace length and noise on the sensitive V_{FBx} node. Take care to route the V_{FBx} trace away from noise sources, such as the inductor or the SWx trace. To improve frequency response, a feedforward capacitor (C_{FF}) can be used.

Channel 1 on the LTC7892 can be programmed to a fixed 28V or 24V output through control of the VPRG1 pin. [Figure 46](#) shows how the V_{FB1} pin is used to sense the output voltage in fixed output mode. Tying VPRG1 to INTV_{CC} or GND programs V_{OUT1} to 28V or 24V, respectively. Floating VPRG1 sets V_{OUT1} to adjustable output mode using external resistors.

The system must be designed so that the V_{FB2} pin voltage is less than 3V. Otherwise, the LTC7892 will enter a 2-phase operation (See [Single Output 2-Phase Operation](#) section for more details). Applications that are most likely to cause this condition are applications where channel 2 is operated in dropout mode with high V_{IN} voltages. For example, R_A and R_B for channel-2 are chosen so that $V_{OUT2} = 8V$ ($R_B/R_A = 5.67$). When V_{IN} is less than 8V, the converter will be regulating, and V_{FB2} will be 1.2V. When V_{IN} is greater than 8V, the converter will be in dropout, and V_{FB2} will be $V_{OUT2}/5.67$. If V_{IN} is greater than 17V, V_{FB2} will be greater than 3V, and the LTC7892 will enter a 2-phase operation, and V_{OUT2} will now be controlled by Channel 1.

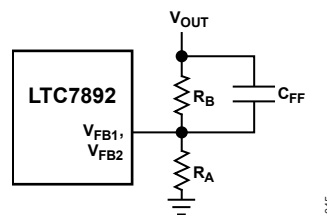


Figure 45. Setting Adjustable Output Voltage

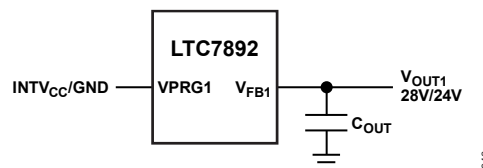


Figure 46. Setting Fixed 28V or 24V Output Voltage

RUNx Pins and Undervoltage Lockout

The two channels of the LTC7892 are enabled using the RUN1 and RUN2 pins. The RUNx pin has a rising threshold of 1.2V with 120mV of hysteresis. Pulling a RUNx pin less than 1.08V shuts down the main control loop and resets the softstart for that channel. Pulling both RUN1 and RUN2 pins less than 0.7V disables the controllers and most internal circuits, including the INTV_{CC} LDO regulators. In this state, the LTC7892 draws only $\approx 1\mu\text{A}$ of current from V_{BIAS}.

The RUNx pins are high impedance and must be externally pulled up, or pulled down, or driven directly by logic. The RUNx pin can tolerate up to 100V (the absolute maximum). Therefore, these pins can be conveniently tied to V_{IN} in applications where the controller is enabled continuously and never shut down. Do not float the RUNx pins.

The RUNx pins can also be configured as precise UVLOs on the input supply with a resistor divider from V_{IN} to ground, as shown in [Figure 47](#).

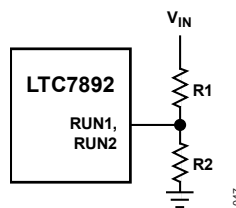


Figure 47. Using the Run Pins as a UVLO

The V_{IN} UVLO thresholds can be computed using Equation 17 and Equation 18, as follows:

$$\text{UVLO RISING} = 1.2\text{V} \left(1 + \frac{R1}{R2} \right) \quad (17)$$

$$\text{ULVO FALLING} = 1.08\text{V} \left(1 + \frac{R1}{R2} \right) \quad (18)$$

The current that flows through the R1 and R2 divider directly adds to the shutdown, sleep, and active current of the LTC7892. Take care to minimize the impact of this current on the overall efficiency of the application circuit. Resistor values in the M Ω range can be required to keep the impact on quiescent shutdown and sleep currents low.

Soft Start (SSx Pins)

The start-up of each V_{OUTx} is controlled by the voltage on the SSx pin (SS1 for channel 1, SS2 for channel 2). When the voltage on the SSx pin is less than the internal 1.2V reference, the LTC7892 regulates the V_{FBx} pin voltage to the voltage on the SSx pin instead of the internal reference.

Soft start is enabled by simply connecting a capacitor from the SSx pin to GND. An internal 12 μA current source charges the capacitor, providing a linear ramping voltage at the SSx pin. The LTC7892 regulates its feedback voltage (and hence V_{OUTx}) according to the voltage on the SSx pin, allowing V_{OUTx} to rise smoothly from 0V to its final regulated value. For a desired soft-start time (t_{SS}), select a soft-start capacitor (C_{SS}) = t_{SS} • 10nF/msec.

INTV_{CC} Regulators (OPTI-DRIVE)

The LTC7892 features two separate internal LDO linear regulators that supply power at the INTV_{CC} pin from either the V_{BIAS} pin or the EXTV_{CC} pin, depending on the EXTV_{CC} pin voltage and connections to the DRVSET and DRVUV pins. The DRV_{CC} pin is the supply pin for the FET gate drivers and must be connected to the INTV_{CC} pin. The V_{BIAS} LDO regulator and the EXTV_{CC} LDO regulator regulate INTV_{CC} between 4V and 5.5V, depending on how the DRVSET pin is set. Each LDO regulator can provide a peak current of at least 100mA.

Bypass the $INTV_{CC}$ pin with a minimum of 4.7 μ F ceramic capacitor placed as close as possible to the pin. It is recommended to place an additional 1 μ F ceramic capacitor next to the DRV_{CC} pin and GND pins to supply the high-frequency transient currents required by the FET gate drivers.

The $DRVSET$ pin programs the $INTV_{CC}$ supply voltage, and the $DRVUV$ pin selects the different $INTV_{CC}$ UVLO and $EXTV_{CC}$ switchover threshold voltages. [Table 6](#) summarizes the different $DRVSET$ pin configurations along with the voltage settings that go with each configuration. [Table 7](#) summarizes the different $DRVUV$ pin configurations and voltage settings. Tying the $DRVSET$ pin to $INTV_{CC}$ programs $INTV_{CC}$ to 5.5V. Tying the $DRVSET$ pin to GND programs $INTV_{CC}$ to 5.0V. Place a 43k Ω to 100k Ω resistor between $DRVSET$ and GND to program the $INTV_{CC}$ voltage between 4V to 5.5V, as shown in [Figure 48](#).

Table 6. $DRVSET$ Pin Configurations and Voltage Settings

$DRVSET$ Pin	$INTV_{CC}$ Voltage (V)
GND	5.0V
$INTV_{CC}$	5.5V
Resistor to GND 43k Ω to 100k Ω	4V to 5.5V

Table 7. $DRVUV$ Pin Configurations and Voltage Settings

$DRVUV$ Pin	$INTV_{CC}$ UVLO Rising and Falling Thresholds (V)	$EXTV_{CC}$ Switchover Rising and Falling Thresholds (V)
GND	3.8V and 3.6V	4.76V and 4.54V
Floating	4.4V and 4.18V	5.95V and 5.56V
$INTV_{CC}$	5V and 4.75V	5.95V and 5.56V

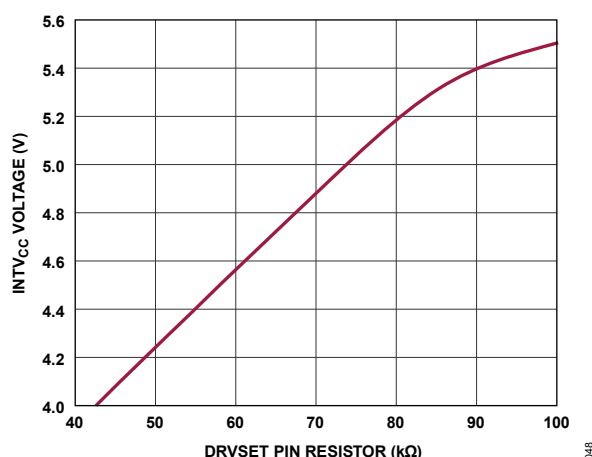


Figure 48. Relationship Between $INTV_{CC}$ Voltage and Resistor Value at the $DRVSET$ Pin

High input voltage applications in which large FETs are being driven at high frequencies can exceed the maximum junction temperature rating for the LTC7892. The $INTV_{CC}$ current, which is dominated by the gate charge current, may be supplied by either the V_{BIAS} LDO regulator or the $EXTV_{CC}$ LDO regulator. When the voltage on the $EXTV_{CC}$ pin is less than its switchover threshold (4.76V or 5.95V, as determined by the $DRVUV$ pin), the V_{BIAS} LDO regulator is enabled.

Power dissipation for the IC, in this case is equal to $V_{BIAS} \cdot INTV_{CC}$ current ($I_{INTV_{CC}}$). The gate charge current is dependent on operating frequency, as discussed in the [Efficiency Considerations](#) section. To estimate the junction temperature, use the equation detailed in [Table 2](#). For example, the LTC7892 $INTV_{CC}$ current is limited to less than 46mA from a 36V supply when not using the $EXTV_{CC}$ supply at a 70°C ambient temperature given by Equation 19.

$$T_J = 70^{\circ}\text{C} + (46\text{mA})(36\text{V})(33^{\circ}\text{C/W}) = 125^{\circ}\text{C} \quad (19)$$

To prevent exceeding the maximum junction temperature, check the input supply current while operating in continuous conduction mode (MODE = $INTV_{CC}$) at maximum V_{BIAS} .

When the voltage applied to $EXTV_{CC}$ rises above its rising switchover threshold, the V_{BIAS} LDO regulator turns off, and the $EXTV_{CC}$ LDO regulator is enabled. The $EXTV_{CC}$ LDO regulator remains on as long as the voltage applied to $EXTV_{CC}$ remains above its falling switchover threshold. The $EXTV_{CC}$ LDO regulator attempts to regulate the $INTV_{CC}$ voltage to the voltage as programmed by the DRVSET pin. Therefore, while $EXTV_{CC}$ is less than the programmed voltage set by the DRVSET pin, the LDO regulator is in dropout, and the $INTV_{CC}$ voltage is approximately equal to $EXTV_{CC}$. When $EXTV_{CC}$ is greater than the programmed voltage (up to an absolute maximum of 30V), $INTV_{CC}$ is regulated to the programmed voltage. If more current is required through the $EXTV_{CC}$ LDO regulator than is specified, add an external Schottky diode between the $EXTV_{CC}$ and $INTV_{CC}$ pins. In this case, do not apply more than 6V to the $EXTV_{CC}$ pin.

Significant efficiency and thermal gains can be realized by powering $INTV_{CC}$ from an external supply. This is accomplished by tying the $EXTV_{CC}$ pin directly to an external supply that is greater than the $INTV_{CC}$ regulation point.

Tying the $EXTV_{CC}$ pin to an 8.5V supply reduces the junction temperature in Equation 15 from 125°C to the results as given by Equation 20, as follows:

$$T_J = 70^{\circ}\text{C} + (46\text{mA})(8.5\text{V})(33^{\circ}\text{C/W}) = 83^{\circ}\text{C} \quad (20)$$

The following list summarizes the three possible connections for $EXTV_{CC}$:

1. $EXTV_{CC}$ grounded. This connection causes the internal V_{BIAS} LDO regulator to power $INTV_{CC}$, resulting in an efficiency penalty of up to 10% or more at high V_{BIAS} voltages.
2. $EXTV_{CC}$ connected directly to V_{IN} . This connection is the normal connection for an application with V_{IN} in the 5V to 30V range and provides significant thermal gains if V_{BIAS} is tied to V_{OUT} .
3. $EXTV_{CC}$ connected directly to an external supply. If an external supply is available in the 5V to 30V range, it can be used to power $EXTV_{CC}$, provided that it is compatible with the FET gate drive requirements. This supply may be higher or lower than V_{BIAS} ; however, a lower $EXTV_{CC}$ voltage results in higher efficiency.

Topside FET Driver Supply (C_B)

External bootstrap capacitors C_B connected to the BOOSTx pins supply the gate drive voltages for the topside FETs. Capacitor C_B in [Figure 34](#) is charged through an internal switch from DRV_{CC} when the SWx pin is low, and the bottom FET is turned on. The on resistance of the internal switch is approximately 7Ω.

When the topside FET is to be turned on, the driver places the C_B voltage across the gate-source of the desired FET, which enhances the FET and turns on the topside switch. The switch node voltage, SWx, rises to V_{OUT} , and the BOOSTx pin follows. With the topside FET on, the boost voltage is more than the output voltage: $V_{BOOST} = V_{OUT} + V_{INTV_{CC}}$. The value of the boost capacitor C_B needs to be 100 times that of the total input capacitance of the topside FETs. For a typical application, a value of $C_B = 0.1\mu\text{F}$ is generally sufficient.

Minimum On-Time Considerations

The minimum on-time ($t_{ON(MIN)}$) is the shortest time duration that the LTC7892 is capable of turning on the bottom FET. $t_{ON(MIN)}$ is determined by internal timing delays and the gate charge required to turn on the bottom FET. Low-duty cycle applications can approach this minimum on-time limit. Ensure the results in Equation 21, as follows:

$$t_{ON(MIN)} < \frac{V_{OUT} - V_{IN}}{V_{OUT} \cdot f} \quad (21)$$

If the duty cycle falls below what can be accommodated by the minimum on-time, the LTC7892 begins to skip cycles. The output voltage continues to regulate, but the ripple voltage and current will increase. The minimum on-time for the LTC7892 is approximately 100ns. If V_{IN} increases, thereby further decreasing the duty cycle, more cycles are skipped, and the LTC7892 can turn on the top FET continuously. If the bottom FET is not turned on frequently enough to recharge the bootstrap capacitor, the top FET will not fully enhance, or it can be completely off when the LTC7892 turns on the top FET. Thus, the LTC7892 cannot achieve 100% top FET on operation.

Fault Conditions: Overtemperature Protection

At higher temperatures, or in cases where the internal power dissipation causes excessive self-heating (such as a short from $INTV_{CC}$ to ground), internal overtemperature shutdown circuitry will shut down the LTC7892. When the internal die temperature exceeds 180°C, the $INTV_{CC}$ LDO regulator and the gate drivers are disabled. When the die cools to 160°C, the LTC7892 enables the $INTV_{CC}$ LDO regulator and resumes operation, beginning with a soft-start startup. Avoid long-term overstress ($T_J > 125^\circ\text{C}$) because it can degrade the performance or shorten the life of the device.

Phase-Locked Loop and Frequency Synchronization

The LTC7892 has an internal PLL that allows the turn-on of the bottom FET of channel 1 to be synchronized to the rising edge of an external clock signal applied to the PLLIN/SPREAD pin. The turn-on of channel 2 bottom FET is 180° out of phase with the external clock.

Rapid phase-locking can be achieved by using the $FREQ$ pin to set a free-running frequency near the desired synchronization frequency. Before synchronization, the PLL is prebiased to the frequency set by the $FREQ$ pin. Consequently, the PLL only needs to make minor adjustments to achieve phase-lock and synchronization. Although it is not required, placing the free-running frequency near the external clock frequency prevents the oscillator from passing through a large range of frequencies as the PLL locks.

When synchronized to an external clock, the LTC7892 operates in pulse-skipping mode if it is selected by the $MODE$ pin, or in forced continuous mode otherwise. The LTC7892 is guaranteed to synchronize to an external clock applied to the PLLIN/SPREAD pin that swings up to at least 2.2V and down to 0.5V or less. Note that the LTC7892 can only be synchronized to an external clock frequency within the range of 100kHz to 3MHz.

Efficiency Considerations

The percent efficiency of a switching regulator is equal to the output power divided by the input power times 100%. Analyzing individual losses is useful for determining what limits the efficiency and which change would produce the most improvement. Percent efficiency can be expressed by Equation 22 as follows:

$$\% \text{Efficiency} = 100\% - (L1 + L2 + L3 + \dots) \quad (22)$$

where $L1$, $L2$, $L3$, and so on, are the individual losses as a percentage of input power.

Although all dissipative elements in the circuit produce losses, four main sources usually account for most of the losses in LTC7892 circuits: IC V_{BIAS} current, $INTV_{CC}$ regulator current, I^2R losses, and bottom-side FET transition losses.

1. The V_{BIAS} current is the DC supply current given in [Table 1](#) (Electrical Characteristics table), which excludes FET drivers and control currents. Other than at very light loads in Burst Mode operation, V_{BIAS} current typically results in a small ($<0.1\%$) loss.
2. The $INTV_{CC}$ current is the sum of the FET driver and control currents. The FET driver current results from switching the gate capacitance of the power FETs. Each time a FET gate is switched from low to high to low again, a packet of charge (dQ) moves from $INTV_{CC}$ to GND. The resulting dQ /time duration (dt) is a current out of $INTV_{CC}$ that is typically much larger than the control circuit current. In continuous mode, gate charge current ($I_{GATECHG}$) = frequency (f) \times ($Q_T + Q_B$), where Q_T and Q_B are the gate charges of the top and bottom FETs.
3. I^2R losses are predicted from the DC resistances of the input fuse (if used), FET, inductor, current sense resistor, and input and output capacitor ESR. In continuous mode, the average output current flows through L and R_{SENSE} , but is chopped between the top and bottom FETs. If the two FETs have approximately the same $R_{DS(ON)}$, the resistance of one FET can simply be summed with the resistances of L , R_{SENSE} , and ESR to obtain the I^2R losses.
4. Transition losses apply only to the bottom FETs and become significant only when operating at higher output voltages (typically 20V or greater) or at high frequency (MHz range). Transition losses can be estimated using Equation 23, as follows:

$$\text{TRANSITION LOSS} = (1.7) \frac{V_{OUT}^3}{V_{IN}} I_{L(MAX)} \cdot C_{MILLER} \cdot f \quad (23)$$

where:

$I_{L(MAX)}$ is the maximum average inductor current.

C_{MILLER} is the Miller capacitance.

f is the operating frequency.

Other hidden losses, such as copper trace and internal battery resistances, can account for an additional 5% to 10% efficiency degradation in portable systems. It is very important to include these system-level losses during the design phase. The internal battery and fuse resistance losses can be minimized by making sure that C_{IN} has adequate charge storage and very low ESR at the switching frequency. A 25W supply typically requires a minimum of 20 μ F to 40 μ F of capacitance having a maximum of 20m Ω to 50m Ω of ESR. Other losses, including inductor core losses, generally account for less than 2% of the total additional loss.

Checking Transient Response

To check the regulator loop response, look at the load current transient response. Switching regulators take several cycles to respond to a step in DC (resistive) load current. When a load step occurs, V_{OUTX} shifts by an amount equal to $\Delta I_{LOAD} \cdot (ESR)$, where ESR is the effective series resistance of C_{OUT} . ΔI_{LOAD} also begins to charge or discharge C_{OUT} , generating the feedback error signal that forces the regulator to adapt to the current change and return V_{OUTX} to its steady-state value. During this recovery time V_{OUTX} can be monitored for excessive overshooting or ringing, which would indicate a stability problem.

OPTI-LOOP compensation allows the transient response to be optimized over a wide range of output capacitance and ESR values. The availability of the ITHx pin not only allows optimization of control loop behavior but also provides a DC-coupled and AC-filtered closed-loop response test point. The DC step, rise time, and settling at this test point truly reflect the closed-loop response. Assuming a predominantly second-order system, the phase margin and/or damping factor can be estimated using the percentage of overshoot seen at the ITHx pin. The bandwidth can also be estimated by examining the rise time at the ITHx pin. The ITHx external components shown in the [Typical Applications](#) section provide an adequate starting point for most applications.

The ITHx series compensation resistor (R_C) and capacitor (C_C) filter set the dominant pole-zero loop compensation. The values can be modified slightly (from 0.5 to 2 times their initial values) to optimize transient response once the final PCB layout is done and the specific output capacitor type and value are determined. The output capacitors must be selected because the various types and values determine the loop gain and phase. An output current pulse of 20% to 80% of full-load current, with a rise time of $1\mu\text{s}$ to $10\mu\text{s}$, produces output voltage and ITHx pin waveforms that will give a sense of the overall loop stability without breaking the feedback loop.

Placing a power FET directly across the output capacitor and driving the gate with an appropriate signal generator is a practical way to produce a realistic load step condition. The initial output voltage step resulting from the step change in output current may not be within the bandwidth of the feedback loop. Therefore, this signal cannot be used to determine the phase margin. For this reason, it is better to look at the ITHx pin signal, which is in the feedback loop and is the filtered and compensated control loop response. The gain of the loop increases by increasing R_C , and the bandwidth of the loop will increase by decreasing C_C . If R_C increases by the same factor that C_C is decreased, the zero frequency is kept the same, keeping the phase shift the same in the most critical frequency range of the feedback loop. The output voltage settling behavior is related to the stability of the closed-loop system and demonstrates the actual overall supply performance.

A second, more severe transient is caused by switching in loads with large ($>1\mu\text{F}$) supply bypass capacitors. The discharged bypass capacitors are effectively put in parallel with C_{OUT} , causing a rapid drop in V_{OUTX} . No regulator can alter its delivery of current quickly enough to prevent this sudden step change in output voltage if the load switch resistance is low and it is driven quickly. If the ratio of C_{LOAD} to C_{OUT} is greater than 1:50, the switch rise time must be controlled so that the load rise time is limited to approximately $C_{LOAD} \cdot 25\mu\text{s}/\mu\text{F}$. Therefore, a $10\mu\text{F}$ capacitor would require a $250\mu\text{s}$ rise time, limiting the charging current to about 200mA.

Design Example

As a design example, assume the nominal input voltage ($V_{IN(NOMINAL)}$) = 12V, $V_{IN(MAX)}$ = 20V, V_{OUTX} = 24V, I_{OUT} = 4A, and f = 1MHz.

Use the following steps to design an application circuit:

1. Set the operating frequency. The frequency is not one of the internal preset values, so a resistor from the FREQ pin to GND is required, with a value given by Equation 24, as follows:

$$R_{FREQ}(\text{in k}\Omega) = \frac{37\text{MHz}}{1\text{MHz}} = 37\text{k}\Omega \quad (24)$$

2. Determine the inductor value. Initially, select a value based on an inductor ripple current of 30%. The inductor value can then be calculated by Equation 25, as follows:

$$L = \frac{V_{IN}}{f \cdot \Delta I_L} \left(1 - \frac{V_{IN}}{V_{OUT}} \right) = 2.4\mu\text{H} \quad (25)$$

The highest value of the ripple current occurs when $V_{IN} = (1/2) \cdot V_{OUT}$. In this case, the ripple at $V_{IN} = 12\text{V}$ is 31%.

3. Verify that the minimum on-time of 100ns is not violated. The minimum on-time occurs at $V_{IN(MAX)}$, as shown in Equation 26:

$$t_{ON(MIN)} < \frac{V_{OUT} - V_{IN(MAX)}}{V_{OUT} \cdot f} = \frac{4\text{V}}{24\text{V} \cdot 1\text{MHz}} = 166\text{ns} \quad (26)$$

This time is sufficient to satisfy the minimum on-time requirement. If the minimum on time is violated, the LTC7892 skips pulses at high input voltage, resulting in lower frequency operation and higher inductor current ripple than desired. If undesirable, this behavior can be avoided by decreasing the frequency (with the inductor value accordingly adjusted) to avoid operation near the minimum on-time.

4. Select the R_{SENSE} resistor value. The peak inductor current is the maximum DC output current plus half the inductor ripple current, or $8\text{A} \times (1 + 0.31 / 2) = 9.24\text{A}$ in this case. The R_{SENSE} resistor value is then calculated based on the minimum value for the maximum current sense threshold (45mV for $\text{ILIM} = \text{float}$) given by Equation 27, as follows:

$$R_{\text{SENSE}} \leq \frac{45\text{mV}}{9.24\text{A}} \approx 4\text{m}\Omega \quad (27)$$

To allow for additional margin, a lower value R_{SENSE} can be used. However, be sure that the inductor saturation current has a sufficient margin above $V_{\text{SENSE(MAX)}} / R_{\text{SENSE}}$, where the maximum value of 55mV is used for $V_{\text{SENSE(MAX)}}$.

5. Select the feedback resistors. Choosing 1% resistors: $R_A = 5\text{k}\Omega$ and $R_B = 95.3\text{k}\Omega$ yields an output voltage of 24.07V. The resistance values selected give a feedback divider current of $24.07\text{V} / (5\text{k}\Omega + 95.3\text{k}\Omega) = 240\mu\text{A}$.
6. Select the FETs. The best way to evaluate FET performance in a particular application is to build and test the circuit on the bench, facilitated by an LTC7892 evaluation board. However, an educated guess about the application is helpful to initially select FETs. Because this is a high current, low voltage application, I^2R losses will likely dominate over transition losses for the bottom FET. Therefore, choose a FET with a lower $R_{\text{DS(ON)}}$ as opposed to a lower gate charge to minimize the combined loss terms. The top FET does not experience transition losses, and its power loss is generally dominated by I^2R losses. For this reason, the top FET is typically chosen to have a lower $R_{\text{DS(ON)}}$ and subsequently, higher gate charge than the bottom FET.
7. When using silicon MOSFETs, be sure to select logic level threshold MOSFETs because the gate drive voltage is limited to 5.5V (INTV_{CC}).
8. Select the output capacitor. C_{OUT} is chosen to filter the square current in the output. The maximum output current peak is given by Equation 28, as follows:

$$I_{\text{OUT(PEAK)}} = I_{\text{OUT(MAX)}} \cdot \left(1 + \frac{\text{RIPPLE}\%}{2}\right) = 4 \cdot \left(1 + \frac{31\%}{2}\right) = 4.62\text{A} \quad (28)$$

A low ESR (5m Ω) capacitor is suggested. This capacitor will limit output voltage ripple to 23.1mV (assuming ESR dominates the ripple).

9. Determine the bias supply components. If another supply is available that is above the INTV_{CC} regulation voltage and below V_{IN} , for example, an 8.5V supply, connect that supply to EXTV_{CC} to improve the efficiency. For a 6.7ms soft start, select a 0.1 μF capacitor for the SSx pin. As a first-pass estimate for the bias components, select the INTV_{CC} capacitance (C_{INTVCC}) = 4.7 μF and boost supply capacitor (C_B) = 0.1 μF .
10. Determine and set application-specific parameters. Set the MODE pin based on the trade-off of light load efficiency and constant frequency operation. Set the PLLIN/SPREAD pin based on whether a fixed, spread spectrum, or phase-locked frequency is desired. The RUNx pin can be used to control the minimum input voltage for regulator operation or can be tied to V_{IN} for always-on operation. Use ITHx compensation components from the typical applications as a first guess, check the transient response for stability, and modify as necessary. Program the DTCA and DTCB pins for the desired dead time delays.

PCB Board Layout Checklist

Figure 49 shows the current waveforms present in the various branches of the synchronous boost converters operating in the continuous mode.

When laying out the printed circuit board, use the following checklist should be used to ensure proper operation of the IC.

Place the top and bottom N-channel FETs (MTOpx and MBOTx) and the high frequency (ceramic) C_{OUTx} capacitors as shown in *Typical Applications* section within 1cm of each other.

Route the TGUPx and TGDNx traces together and connect them as close as possible to the top FET gate. Route the BGDNx and BGUPx traces together and connect them as close as possible to the bottom FET gate. If using gate resistors, connect the resistor connections to the FET gate as close as possible to the FET. Connecting TGUPx and TGDNx further away from the top FET gate, as well as connecting BGUPx and BGDNx further away from the bottom FET gate, can adversely affect the operation of the LTC7892's adaptive dead time control.

The combined IC GND pin and the GND return of C_{INTVCC} must return to the combined C_{OUT} negative terminals. The path formed by the bottom N-channel FET and the C_{IN} capacitor must have short leads and PCB trace lengths. Connect the output capacitor's negative terminals as close as possible to the negative terminals of the input capacitor by placing the capacitors next to each other and away from the loop.

Connect the LTC7892 V_{FBx} pin resistive dividers to the positive terminals of C_{OUT} and the signal GND. Place the divider close to the V_{FBx} pin to minimize noise coupling into the sensitive V_{FBx} node. The feedback resistor connections must not be along the high-current input feeds from the input capacitors.

Route the SENSEx⁻ and SENSEx⁺ leads together with minimum PCB trace spacing. Route these traces away from the high-frequency switching nodes on an inner layer, if possible. The filter capacitor between SENSEx⁺ and SENSEx⁻ must be as close as possible to the IC. Ensure accurate current sensing with Kelvin connections at the sense resistor.

Connect the INTV_{CC} decoupling capacitor close to the IC, between the INTV_{CC} and the power GND pin. This capacitor carries the current peaks of the FET drivers. Place an additional 1 μ F ceramic capacitor next to the DRV_{CC} and GND pins to help improve noise performance.

Keep the switching nodes (SW1 and SW2), top gate nodes (TGUP1/TGDN1 and TGUP2/TGDN2), and boost nodes (BOOST1 and BOOST2) away from sensitive small-signal nodes, especially from the voltage and current sensing feedback pins of the other channel. All of these nodes have large and fast-moving signals. Therefore, keep these nodes on the output side of the LTC7892 and ensure they occupy the minimum PCB trace area.

Use a modified star ground technique: a low impedance, large copper area central grounding point on the same side of the PCB as the input and output capacitors, with tie-ins for the bottom of the INTV_{CC} decoupling capacitor, the bottom of the voltage feedback resistive divider, and the GND pin of the IC.

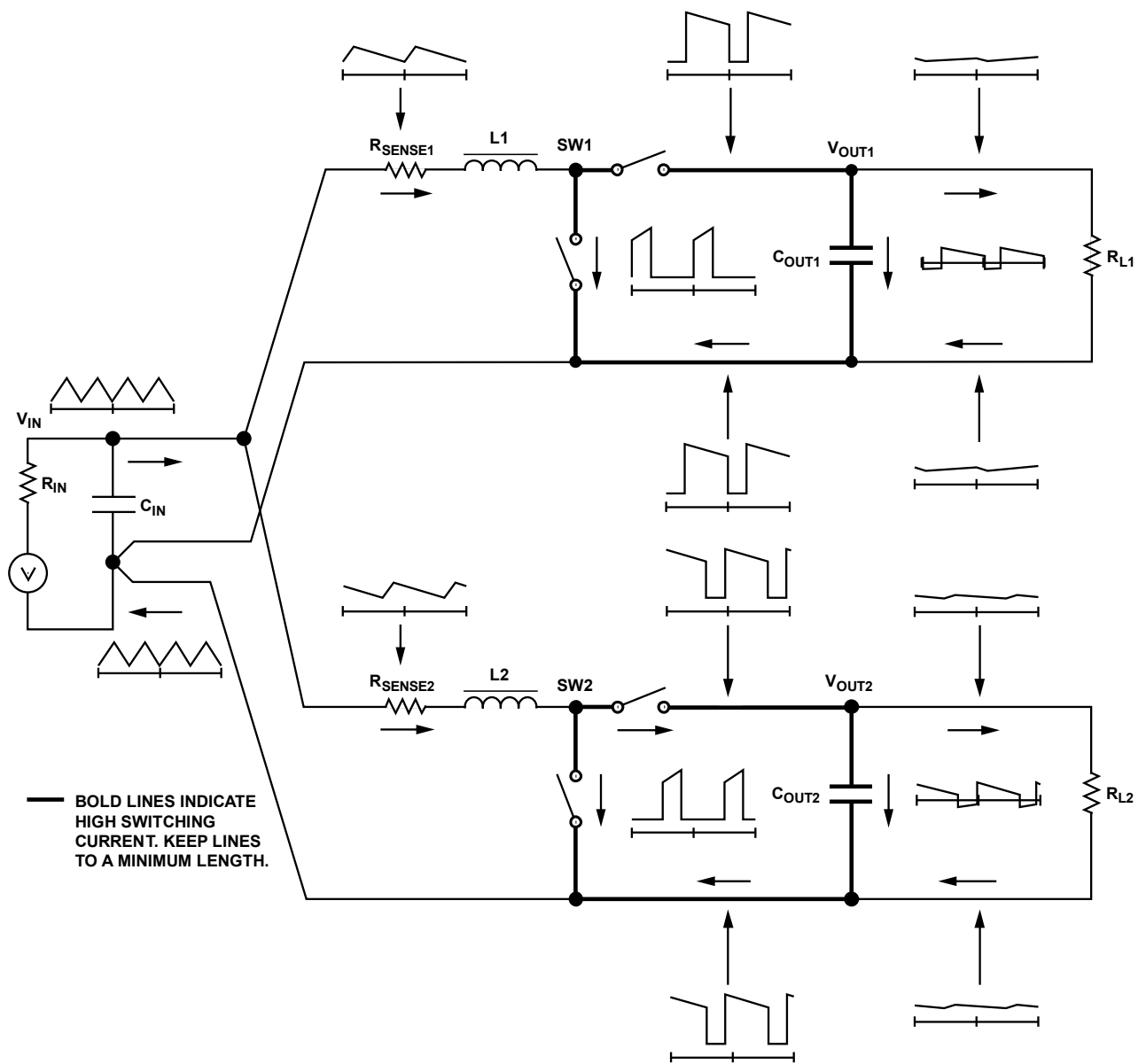


Figure 49. Branch Current Waveforms

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PCB Layout Debugging

Start with one channel on at a time. Use a DC to 50 MHz current probe to monitor the current in the inductor while testing the circuit. Monitor the output switching node (the SWx pin) to synchronize the oscilloscope to the internal oscillator and probe the actual output voltage as well. Check for proper performance over the operating voltage and current range expected in the application. The frequency of operation is maintained over the input voltage range down to dropout and until the output load drops to less than the low current operation threshold, typically 25% of the maximum designed current level in Burst Mode operation.

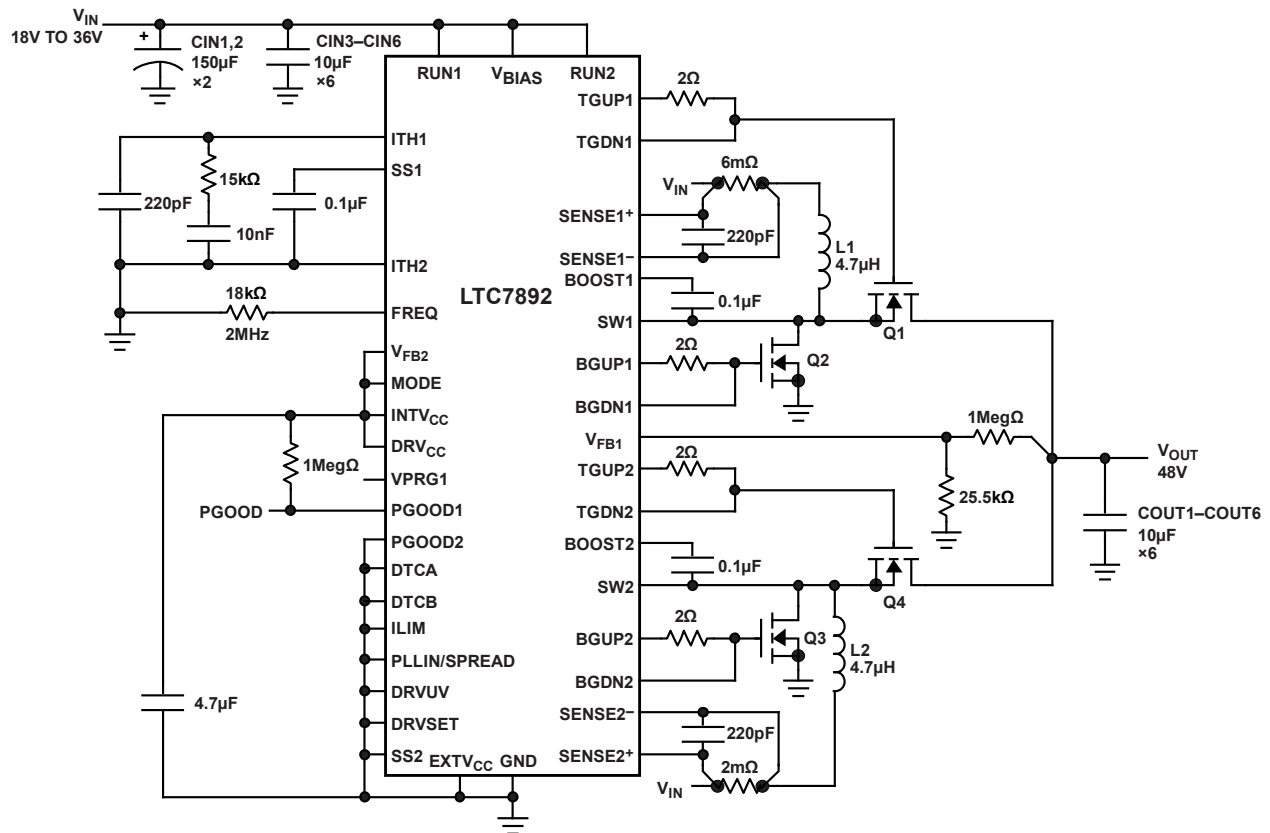
The duty-cycle percentage is maintained from cycle to cycle in a well-designed, low-noise PCB implementation. Variation in the duty cycle at a subharmonic rate can suggest noise pickup at the current or voltage sensing inputs or inadequate loop compensation. Overcompensation of the loop can tame an improper PCB layout if regulator bandwidth optimization is not required. Turn on both controllers at the same time after each controller is checked for its individual performance. A particularly difficult region of operation is when one controller channel is nearing its current comparator trip point when the other channel is turning on its top FET, which occurs around 50% duty cycle on either channel due to the phasing of the internal clocks and may cause minor duty-cycle jitter.

Reduce V_{BIAS} from its nominal level to verify the operation of the regulator at the maximum duty cycle. Check the operation of the undervoltage lockout circuit by further lowering V_{BIAS} while monitoring the outputs to verify operation.

Investigate whether any problems exist only at higher output currents or only at higher input voltages. If problems coincide with high input voltages and low output currents, look for capacitive coupling between the BOOSTx, SWx, TGxxx, and possibly BGxxx connections and the sensitive voltage and current pins. Place the capacitor across the current sensing pins next to the pins of the IC. This capacitor helps to minimize the effects of differential noise injection due to high-frequency capacitive coupling. If problems are encountered with high current output loading at lower input voltages, look for inductive coupling between C_{IN} , the top FET, and the bottom FET components to the sensitive current and voltage sensing traces. In addition, investigate the common GND path voltage pickup between these components and the GND pin of the IC.

A problem that may be missed in an otherwise properly working switching regulator results when the current sensing leads are hooked up backward. The output voltage under this improper hookup is maintained, but the advantages of current mode control are not realized. Compensation of the voltage loop is more sensitive to component selection. This behavior can be investigated by temporarily shorting out the current sensing resistor. The regulator maintains control of the output voltage even during this condition.

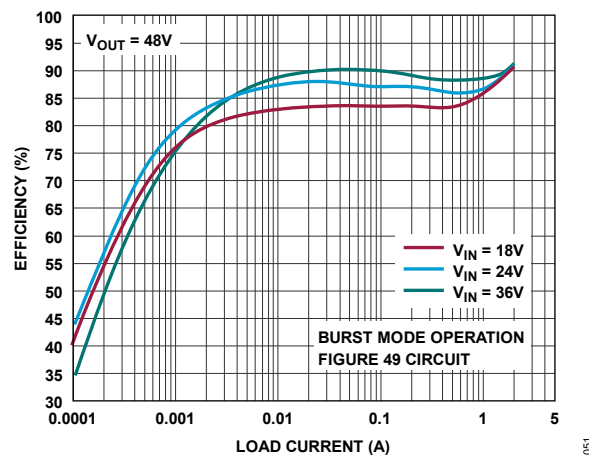
TYPICAL APPLICATIONS



CIN1, CIN2: PANASONIC EEH-ZU1H151P
 CIN3-CIN6: MURATA GRM32ER71H106KA12L
 COUT1-COUT6: MURATA GRM32EC72A106KE05L
 L1, L2: COILCRAFT XGL6060-472
 Q1-Q4: EPC EPC2204A

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Figure 50. High Frequency (2MHz), Dual-Phase, Single 48V Output Boost Converter Using GaN FETs



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Figure 51. Efficiency vs Load Current for Figure 50

RELATED PARTS

PART NUMBER	DESCRIPTION	COMMENTS
LTC3788	38V, Multiphase Dual Output Synchronous Step-Up Controller	4.5V (Down to 2.5V After Start-Up) $\leq V_{IN} \leq 38V$, V_{OUT} Up to 60V, PLL Fixed Frequency of 50kHz to 900kHz, 5mm \times 5mm, QFN-32, SSOP-28
LTC3897	65V, PolyPhase Synchronous Boost Controller with Input/Output Protection	4.5V $\leq V_{IN} \leq 65V$, 75V Peak, V_{OUT} Up to 60V, PLL Fixed Frequency 75kHz to 550kHz, $I_Q = 55\mu A$, TSSOP-38, 5mm \times 7mm, QFN-38
LTC3786	38V, Low I_Q Synchronous Boost Controller with PassThru	4.5V (Down to 2.5V After Start-Up) $\leq V_{IN} \leq 38V$, V_{OUT} Up to 60V, PLL fixed frequency of 50kHz to 900kHz, 3mm \times 3mm, QFN-32, MSOP-16E
LTC3787	38V, Multiphase, Dual Channel Synchronous Boost Controller with PassThru	4.5V (Down to 2.5V After Start-Up) $\leq V_{IN} \leq 38V$, V_{OUT} Up to 60V, PLL Fixed Frequency of 50kHz to 900kHz, 4mm \times 5mm, QFN-28, SSOP-28
LTC3784	60V, Low I_Q , Multiphase Synchronous Boost Controller with PassThru	4.5V (Down to 2.5V After Start-Up) $\leq V_{IN} \leq 60V$, V_{OUT} Up to 60V, PLL Fixed Frequency of 50kHz to 900kHz, $I_Q = 28\mu A$, 4mm \times 5mm, QFN-28, SSOP-28
LTC7890	100V, Low I_Q , Dual, 2-Phase Synchronous Step-Down Controller for GaN FETs	4V $\leq V_{IN} \leq 100V$, V_{OUT} Up to 60V, PLL Fixed Frequency of 100kHz to 3MHz, $I_Q = 5\mu A$, 6mm \times 6mm, QFN-40 (Side Wettable)
LTC7891	100V, Low I_Q , Synchronous Step-Down Controller for GaN FETs	4V $\leq V_{IN} \leq 100V$, 0.8 $\leq V_{OUT} \leq 60V$, PLL Fixed Frequency of 100kHz to 3MHz, $I_Q = 5\mu A$, 4mm \times 5mm, QFN-28 (Side Wettable)
LTC7893	100V, Low I_Q , Synchronous Boost Controller for GaN FETs	4V (Down to 1V After Start-Up) $\leq V_{IN} \leq 60V$, V_{OUT} Up to 100V, PLL Fixed Frequency of 100kHz to 3MHz, $I_Q = 15\mu A$, 4mm \times 5mm, QFN-28 (Side Wettable)
LT8418	100V, Half-Bridge GaN Driver with Smart Integrated Bootstrap Switch	3.85V to 5.5V Operation, 4A/0.6 Ω Peak Pull-up, 8A/0.2 Ω Peak Pull-down, 10ns (typ) Propagation Delay, 1.67mm \times 1.67mm, 12-Ball WLCSP

UJM Package
40-Lead Plastic Side Wetable QFN (6mm x 6mm)
 (Reference LTC DWG # 05-08-1681 Rev Ø)

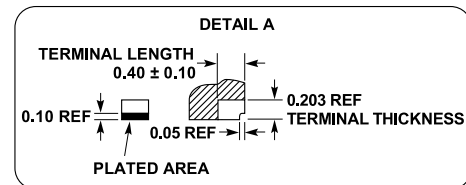


Diagram illustrating the top view of a package with dimensions and tolerances:

- Overall width: 6.50 ± 0.05
- Overall height: 6.50 ± 0.05
- Inner width: 4.10 ± 0.05
- Inner height: 4.10 ± 0.05
- Distance from top edge to first row of pins: 0.70 ± 0.05
- Distance between rows of pins: 4.50 ± 0.05 (4 SIDES)
- Pin pitch: 0.25 ± 0.05
- Pin width: 0.50 BSC
- Label: PACKAGE OUTLINE

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ORDERING GUIDE

Table 8. Ordering Guide

LEAD-FREE FINISH	TAPE AND REEL	PART MARKING	PACKAGE DESCRIPTION	TEMPERATURE RANGE
LTC7892AUJM#PBF	LTC7892AUJM#TRPBF	LTC7892 UJM	40-Lead QFN (6mm × 6mm, Plastic Side Wettable)	–40°C to 125°C
AUTOMOTIVE PRODUCTS*				
LTC7892AUJM#WPBF	LTC7892AUJM#WTRPBF	LTC7892 UJM	40-Lead QFN (6mm × 6mm, Plastic Side Wettable)	–40°C to 125°C

Contact the factory for parts specified with wider operating temperature ranges.

Tape and reel specifications. Some packages are available in 500 unit reels through designated sales channels with the #TRMPBF suffix.

*Versions of this part are available with controlled manufacturing to support the quality and reliability requirements of automotive applications. These models are designated with a #W suffix. Only the automotive grade products shown are available for use in automotive applications. Contact your local Analog Devices account representative for specific product ordering information and to obtain the specific Automotive Reliability reports for these models.

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